TMUX810x 具有闩锁效应抑制和 1.8V 逻辑电平的 100V、扁平 R_{ON}、单路 8:1 和双路 4:1 多路复用器

1 特性

- 支持高电源电压：
  - 双电源：±10V 至 ±50V
  - 单电源：10V 至 100V
  - 非对称双电源运行
- 在整个电源电压范围内提供一致的参数性能
- 闩锁效应抑制
- 低串扰：-110dB
- 低输入泄漏电流：40pA
- 低导通电阻平坦度：0.5Ω
- 无需额外逻辑轨 (V_L)
- 支持 1.8V 逻辑电平
- 失效防护逻辑：高达 48V（与电源无关）
- 逻辑引脚上的集成下拉电阻器
- 双向信号路径
- 先断后合开关
- 宽工作温度 T_A：–40°C 至 125°C
- 业界通用的 TSSOP 封装和
  较小的 WQFN 封装

2 应用

- 高电压双向切换
- 模拟和数字多路复用和多路信号分离
- 半导体测试设备
- LCD 测试设备
- 电池测试设备
- 数据采集系统 (DAQ)
- 数字万用表 (DMM)
- 工厂自动化和控制
- 可编程逻辑控制器 (PLC)
- 模拟输入模块

3 说明

TMUX8108 和 TMUX8109 是支持高电压的现代模拟多路复用器，可采用 8:1（单端）和 4:1（差分）配置。此器件可在双电源、单电源或非对称电源供电时正常运行，最大电源电压为 100V。TMUX810x 器件可在整个电源电压范围内提供一致的模拟参数性能。TMUX8108 和 TMUX8109 可在源极 (Sx) 和漏极 (D) 引脚上支持双向模拟和数字信号。

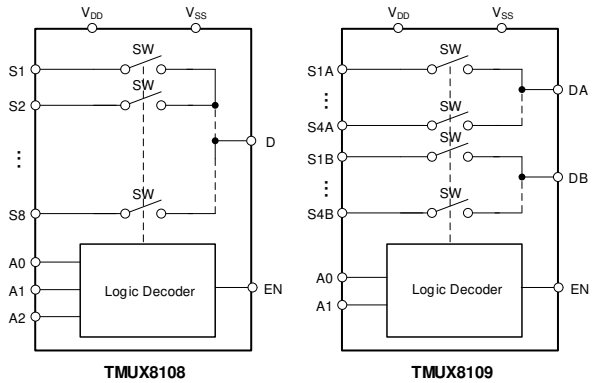
所有逻辑输入均支持 1.8V、3.3V、5V 的逻辑电平，并可在电压高达 48V 时进行连接，从而通过控制信号电压实现系统灵活性。失效防护逻辑电路允许在施加电源引脚上的电压之前，先施加逻辑引脚上的电压，从而保护器件免受潜在的损害。

此器件系列具有闩锁效应抑制功能，可防止器件内寄生结构之间的大电流不良事件。闩锁状态通常会一直持续到电源轨关闭为止，并可能导致器件故障。凭借闩锁效应抑制功能，此系列多路复用器能够在恶劣的环境中使用。

器件信息

器件型号(1)	封装	封装尺寸（标称值）
TMUX8108 TMUX8109	TSSOP (16)	5.00mm × 4.40mm
	WQFN (16)(2)	4.00mm × 4.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。
(2) 预发布封装。



TMUX8108 和 TMUX8109 方框图

本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。有关适用的官方英文版本的最新信息，请访问 www.ti.com，其内容始终优先。TI 不保证翻译的准确性和有效性。在实际设计之前，请务必参考最新版本的英文版本。

Table of Contents

1 特性 1
2 应用 1
3 说明 1
4 Revision History 2
5 Device Comparison Table 3
6 Pin Configuration and Functions 3
7 Specifications 5
7.1 Absolute Maximum Ratings: TMUX810x Devices 5
7.2 ESD Ratings 5
7.3 Recommended Operating Conditions: TMUX810x Devices 6
7.4 Thermal Information 6
7.5 Electrical Characteristics (Global): TMUX810x Devices 7
7.6 Electrical Characteristics (±15-V Dual Supply) 7
7.7 Electrical Characteristics (±36-V Dual Supply) 9
7.8 Electrical Characteristics (±50-V Dual Supply) 10
7.9 Electrical Characteristics (72-V Single Supply) 11
7.10 Electrical Characteristics (100-V Single Supply) 12
7.11 Switching Characteristics: TMUX810x Devices 13
7.12 Typical Characteristics 14
8 Parameter Measurement Information 19
8.1 On-Resistance 19
8.2 Off-Leakage Current 19
8.3 On-Leakage Current 20
8.4 Break-Before-Make Delay 20
8.5 Enable Turn-on and Turn-off Time 21
8.6 Transition Time 21
8.7 Charge Injection 22
8.8 Off Isolation 22
8.9 Crosstalk 23
8.10 Bandwidth 24
8.11 THD + Noise 24
9 Detailed Description 26
9.1 Overview 26
9.2 Functional Block Diagram 26
9.3 Feature Description 26
9.4 Device Functional Modes 28
10 Application and Implementation 29
10.1 Application Information 29
10.2 Typical Application 29
11 Power Supply Recommendations 31
12 Layout 31
12.1 Layout Guidelines 31
12.2 Layout Example 32
13 Device and Documentation Support 33
13.1 Documentation Support 33
13.2 接收文档更新通知 33
13.3 支持资源 33
13.4 Trademarks 33
13.5 Electrostatic Discharge Caution 33
13.6 术语表 33
14 Mechanical, Packaging, and Orderable Information 33

4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision * (September 2021) to Revision A (December 2021)	Page
• 将数据表的状态从*预告信息*更改为*量产数据*	1

Copyright © 2022 Texas Instruments Incorporated

5 Device Comparison Table

PRODUCT	DESCRIPTION
TMUX8108	Single channel 8:1 multiplexer
TMUX8109	Dual channel 4:1 multiplexer

6 Pin Configuration and Functions

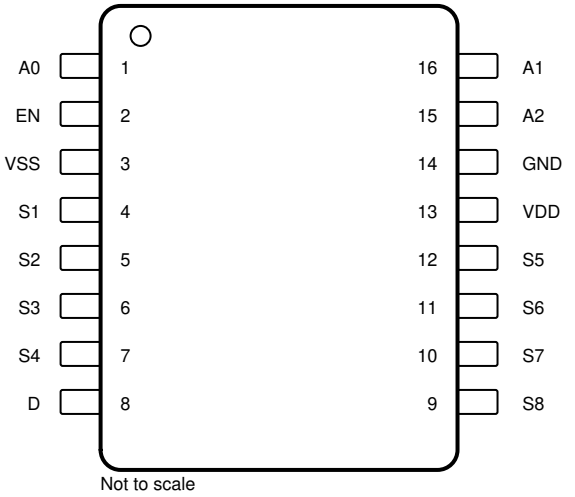


图 6-1. PW Package 16-Pin TSSOP Top View

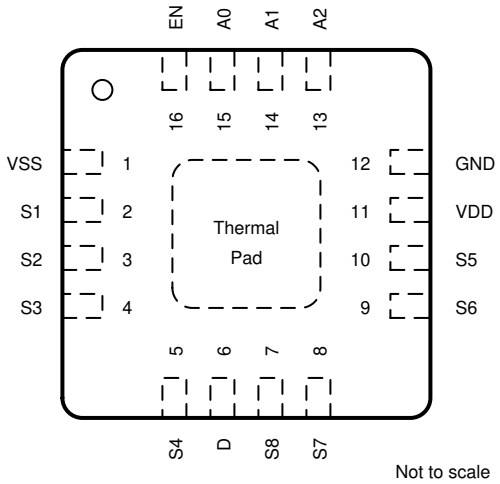


图 6-2. RUM Package 16-Pin WQFN Top View

表 6-1. Pin Functions: TMUX8108

PIN			TYPE(1)	DESCRIPTION
NAME	TSSOP	WQFN		
A0	1	15	I	Logic control input address 0 (A0).
EN	2	16	I	Active high digital enable (EN) pin. The device is disabled and all switches become high impedance when the pin is low. When the pin is high, the Ax logic inputs determine individual switch states.
V_{SS}	3	1	P	Negative power supply. This pin is the most negative power-supply potential. In single-supply applications, this pin can be connected to ground. For reliable operation, connect a decoupling capacitor ranging from 0.1 µF to 10 µF between V_{SS} and GND.
S1	4	2	I/O	Source pin 1. Can be an input or output.
S2	5	3	I/O	Source pin 2. Can be an input or output.
S3	6	4	I/O	Source pin 3. Can be an input or output.
S4	7	5	I/O	Source pin 4. Can be an input or output.
D	8	6	I/O	Drain pin. Can be an input or output.
S8	9	7	I/O	Source pin 8. Can be an input or output.
S7	10	8	I/O	Source pin 7. Can be an input or output.
S6	11	9	I/O	Source pin 6. Can be an input or output.
S5	12	10	I/O	Source pin 5. Can be an input or output.
V_{DD}	13	11	P	Positive power supply. This pin is the most positive power-supply potential. For reliable operation, connect a decoupling capacitor ranging from 0.1 µF to 10 µF between V_{DD} and GND.
GND	14	12	P	Ground (0 V) reference
A2	15	13	I	Logic control input address 2 (A2).
A1	16	14	I	Logic control input address 1 (A1).
Thermal Pad			—	The thermal pad is not connected internally. It is recommended that the pad be tied to GND or VSS for the best performance.

(1) I = input, O = output, I/O = input and output, P = power

Copyright © 2022 Texas Instruments Incorporated

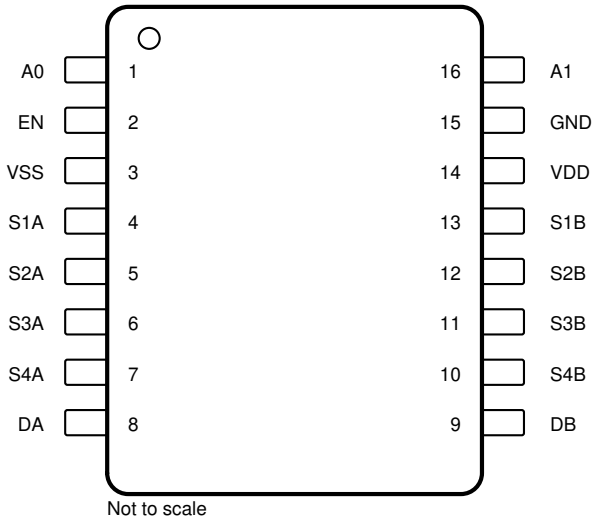


图 6-3. PW Package 16-Pin TSSOP Top View

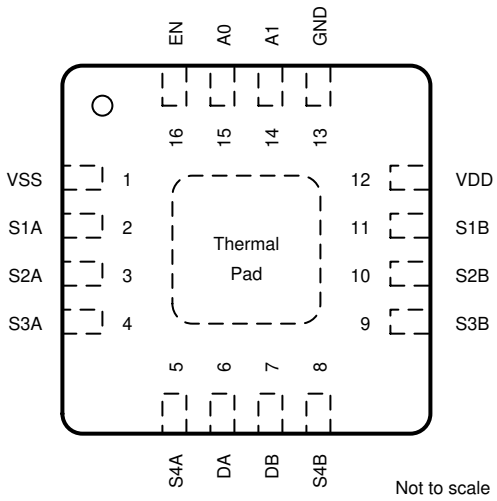


图 6-4. RUM Package 16-Pin WQFN Top View

表 6-2. Pin Functions: TMUX8109

PIN			TYPE(1)	DESCRIPTION
NAME	TSSOP	WQFN		
A0	1	15	I	Logic control input address 0 (A0).
EN	2	16	I	Active high digital enable (EN) pin. The device is disabled and all switches become high impedance when the pin is low. When the pin is high, the Ax logic inputs determine individual switch states.
V_{SS}	3	1	P	Negative power supply. This pin is the most negative power-supply potential. In single-supply applications, this pin can be connected to ground. For reliable operation, connect a decoupling capacitor ranging from 0.1 µF to 10 µF between V_{SS} and GND.
S1A	4	2	I/O	Source pin 1A. Can be an input or output.
S2A	5	3	I/O	Source pin 2A. Can be an input or output.
S3A	6	4	I/O	Source pin 3A. Can be an input or output.
S4A	7	5	I/O	Source pin 4A. Can be an input or output.
DA	8	6	I/O	Drain terminal A. Can be an input or output.
DB	9	7	I/O	Drain terminal B. Can be an input or output
S4B	10	8	I/O	Source pin 4B. Can be an input or output.
S3B	11	9	I/O	Source pin 3B. Can be an input or output.
S2B	12	10	I/O	Source pin 2B. Can be an input or output.
S1B	13	11	I/O	Source pin 1B. Can be an input or output.
V_{DD}	14	12	P	Positive power supply. This pin is the most positive power-supply potential. For reliable operation, connect a decoupling capacitor ranging from 0.1 µF to 10 µF between V_{DD} and GND.
GND	15	13	P	Ground (0 V) reference
A1	16	14	I	Logic control input address 1 (A1).
Thermal Pad			—	The thermal pad is not connected internally. It is recommended that the pad be tied to GND or VSS for the best performance.

(1) I = input, O = output, I/O = input and output, P = power

Copyright © 2022 Texas Instruments Incorporated

7 Specifications

7.1 Absolute Maximum Ratings: TMUX810x Devices

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V_{DD} – V_{SS}	Supply voltage		110	V
V_{DD}		– 0.5	110	V
V_{SS}		– 110	0.5	V
V_{Ax} or V_{EN}	Logic control input pin voltage (Ax, EN)	– 0.5	50	V
I_{Ax} or I_{EN}	Logic control input pin current (Ax, EN)	– 30	30	mA
V_S or V_D	Source or drain voltage (Sx, D)	V_{SS} – 2	V_{DD}+2	V
$I_{DC\ (CONT)}$	Source or drain continuous current (Sx, D)	– 100	100	mA
I_{IK} (2)	Diode clamp current at 85°C	– 100	100	mA
	Diode clamp current at 125°C	– 15	15	mA
T_{stg}	Storage temperature	– 65	150	°C
T_A	Ambient temperature	– 55	150	°C
T_J	Junction temperature		150	°C
P_{tot} (3)	Total power dissipation (TSSOP)		720	mW

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) Pins are diode-clamped to the power-supply rails. Over voltage signals must be voltage and current limited to maximum ratings.
(3) For TSSOP package: P_{tot} derates linearly above T_A = 70°C by 10.5 mW/°C

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002, all pins(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Copyright © 2022 Texas Instruments Incorporated

7.3 Recommended Operating Conditions: TMUX810x Devices

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_{DD} – V_{SS} (1)	Power supply voltage differential		10		100	V
V_{DD}	Positive power supply voltage		10		100	V
V_S or V_D (2)	Signal path input/output voltage (source or drain pin)		V_{SS}		V_{DD}	V
V_A or V_{EN}	Address or enable pin voltage		0		48	V
T_A	Ambient temperature		–40		125	°C
V_S or V_D (2)	Signal path input/output voltage (source or drain pin)		V_{SS}		V_{DD}	V
T_A	Ambient temperature		–40		125	°C
I_{DC} 1ch.(3)	Continuous current through switch for TSSOP or QFN on 1 channel				100	mA
I_{DC} All ch.(4)	Continuous current through switch on all channels at the same time, TSSOP package	T_A = 25°C			75	mA
		T_A = 85°C			50	mA
		T_A = 125°C			25	mA

(1) V_{DD} and V_{SS} can be any value as long as 10 V ⩽ (V_{DD} – V_{SS}) ⩽ 100 V, and the minimum V_{DD} is met.
(2) V_S or V_D is the voltage on any Source or Drain pins.
(3) Max continuous current shown for a single channel at a time.
(4) Max continuous current shown for all channels at a time. Refer to max power dissipation (P_{tot}) to ensure package limitations are not violated.

7.4 Thermal Information

THERMAL METRIC(1)		TMUX8108	TMUX8109	UNIT
		PW (TSSOP)	PW (TSSOP)	
		16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	97.0	96.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	26.7	26.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.8	43.1	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	1.1	1.1	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	43.1	42.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Copyright © 2022 Texas Instruments Incorporated

7.5 Electrical Characteristics (Global): TMUX810x Devices

over operating free-air temperature range (unless otherwise noted)
typical at V_{DD} = +36 V, V_{SS} = – 36 V, GND = 0 V and T_A = 25℃ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
LOGIC INPUTS							
V_{IH}	Logic voltage high		– 40°C to +125°C	1.3		48	V
V_{IL}	Logic voltage low		– 40°C to +125°C	0		0.8	V
I_{IH}	Input leakage current	Logic inputs = 0 V, 5 V, or 48 V	– 40°C to +125°C		0.4	3.8	µA
I_{IL}	Input leakage current	Logic inputs = 0 V, 5 V, or 48 V	– 40°C to +125°C	– 0.2	– 0.005		µA
C_{IN}	Logic input capacitance		– 40°C to +125°C		3		pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic inputs = 0 V, 5 V, or 48 V	25°C		250	500	µA
			– 40°C to +85°C			500	µA
			– 40°C to +125°C			500	µA
I_{SS}	V_{SS} supply current	Logic inputs = 0 V, 5 V, or 48 V	25°C		250	420	µA
			– 40°C to +85°C			420	µA
			– 40°C to +125°C			420	µA

7.6 Electrical Characteristics (±15-V Dual Supply)

V_{DD} = +15 V ± 10%, V_{SS} = – 15 V ± 10%, GND = 0 V (unless otherwise noted)
Typical at T_A = 25℃ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = – 10 V to +10 V I_D = – 5 mA	25°C		38	55	Ω
			– 40°C to +85°C			75	Ω
			– 40°C to +125°C			90	Ω
ΔR_{ON}	On-resistance mismatch between channels	V_S = – 10 V to +10 V I_D = – 5 mA	25°C		0.65		Ω
			– 40°C to +85°C			1.5	Ω
			– 40°C to +125°C			2.1	Ω
$R_{ON\ FLAT}$	On-resistance flatness	V_S = – 10 V to +10 V I_D = – 5 mA	25°C		0.5		Ω
$R_{ON\ DRIFT}$	On-resistance drift	V_S = 0 V, I_S = – 5 mA	– 40°C to +125°C		0.25		Ω/°C
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 16.5 V, V_{SS} = – 16.5 V Switch state is off V_S = +10 V / – 10 V V_D = – 10 V / +10 V	25°C		0.01		nA
			– 40°C to +85°C	– 3		3	nA
			– 40°C to +125°C	– 15		15	nA
$I_{D(OFF)}$	Drain off leakage current(1)	V_{DD} = 16.5 V, V_{SS} = – 16.5 V Switch state is off V_S = +10 V / – 10 V V_D = – 10 V / +10 V	25°C		0.04		nA
			– 40°C to +85°C	– 8		8	nA
			– 40°C to +125°C	– 40		40	nA
$I_{S(ON)}$ $I_{D(ON)}$	Channel on leakage current(2)	V_{DD} = 16.5 V, V_{SS} = – 16.5 V Switch state is on V_S = V_D = ±10 V	25°C		0.04		nA
			– 40°C to +85°C	– 8		8	nA
			– 40°C to +125°C	– 40		40	nA
$\Delta I_{S(ON)}$ $\Delta I_{D(ON)}$	Leakage current mismatch between channels(2)	V_{DD} = 16.5 V, V_{SS} = – 16.5 V Switch state is on V_S = V_D = ±10 V	25°C		5		pA
			85°C		50		pA
			125°C		900		pA

(1) When V_S is positive,V_D is negative. And when V_S is negative, V_D is positive.

Copyright © 2022 Texas Instruments Incorporated

(2) When V_S is at a voltage potential, V_D is floating. And when V_D is at a voltage potential, V_S is floating.

Copyright © 2022 Texas Instruments Incorporated

7.7 Electrical Characteristics (±36-V Dual Supply)

V_{DD} = +36 V ± 10%, V_{SS} = – 36 V ± 10%, GND = 0 V (unless otherwise noted)
Typical at T_A = 25℃ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = -25 V to +25 V I_D = – 5 mA	25°C		38	48	Ω
			– 40°C to +85°C			65	
			– 40°C to +125°C			80	
ΔR_{ON}	On-resistance mismatch between channels	V_S = -25 V to +25 V I_D = – 5 mA	25°C		0.65		Ω
			– 40°C to +85°C			1.5	
			– 40°C to +125°C			2.1	
$R_{ON\ FLAT}$	On-resistance flatness	V_S = -25 V to +25 V I_D = – 5 mA	25°C		0.9		Ω
$R_{ON\ DRIFT}$	On-resistance drift	V_S = 0 V, I_S = – 5 mA	– 40°C to +125°C		0.25		Ω/°C
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 39.6 V, V_{SS} = – 39.6 V Switch state is off V_S = +25 V / – 25 V V_D = – 25 V / +25 V	25°C		0.01		nA
			– 40°C to +85°C	– 3		3	
			– 40°C to +125°C	– 15		15	
$I_{D(OFF)}$	Drain off leakage current(1)	V_{DD} = 39.6 V, V_{SS} = – 39.6 V Switch state is off V_S = +25 V / – 25 V V_D = – 25 V / +25 V	25°C		0.06		nA
			– 40°C to +85°C	– 8		8	
			– 40°C to +125°C	– 40		40	
$I_{S(ON)}$ $I_{D(ON)}$	Channel on leakage current(2)	V_{DD} = 39.6 V, V_{SS} = – 39.6 V Switch state is on V_S = V_D = ±25 V	25°C		0.06		nA
			– 40°C to +85°C	– 8		8	
			– 40°C to +125°C	– 40		40	
$\Delta I_{S(ON)}$ $\Delta I_{D(ON)}$	Leakage current mismatch between channels(2)	V_{DD} = 39.6 V, V_{SS} = – 39.6 V Switch state is on V_S = V_D = ±25 V	25°C		5		pA
			85°C		30		
			125°C		100		

(1) When V_S is positive,V_D is negative. And when V_S is negative, V_D is positive.
(2) When V_S is at a voltage potential, V_D is floating. And when V_D is at a voltage potential, V_S is floating.

Copyright © 2022 Texas Instruments Incorporated

7.8 Electrical Characteristics (±50-V Dual Supply)

V_{DD} = +50 V, V_{SS} = – 50 V, GND = 0 V (unless otherwise noted)
Typical at T_A = 25℃ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = – 45 V to +45 V I_D = – 5 mA	25°C		38	48	Ω
			– 40°C to +85°C			65	
			– 40°C to +125°C			80	
ΔR_{ON}	On-resistance mismatch between channels	V_S = – 45 V to +45 V I_D = – 5 mA	25°C		0.65		Ω
			– 40°C to +85°C			1.5	
			– 40°C to +125°C			2.1	
$R_{ON\ FLAT}$	On-resistance flatness	V_S = – 45 V to +45 V I_D = – 5 mA	25°C		1		Ω
$R_{ON\ DRIFT}$	On-resistance drift	V_S = 0 V, I_S = – 5 mA	– 40°C to +125°C		0.25		Ω/°C
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 50 V, V_{SS} = – 50 V Switch state is off V_S = +45 V / – 45 V V_D = – 45 V / +45 V	25°C		0.02		nA
			– 40°C to +85°C	– 3		3	
			– 40°C to +125°C	– 15		15	
$I_{D(OFF)}$	Drain off leakage current(1)	V_{DD} = 50 V, V_{SS} = – 50 V Switch state is off V_S = +45 V / – 45 V V_D = – 45 V / +45 V	25°C		0.09		nA
			– 40°C to +85°C	– 8		8	
			– 40°C to +125°C	– 40		40	
$I_{S(ON)}$ $I_{D(ON)}$	Channel on leakage current(2)	V_{DD} = 50 V, V_{SS} = – 50 V Switch state is on V_S = V_D = ±45 V	25°C		0.09		nA
			– 40°C to +85°C	– 8		8	
			– 40°C to +125°C	– 40		40	
$\Delta I_{S(ON)}$ $\Delta I_{D(ON)}$	Leakage current mismatch between channels(2)	V_{DD} = 50 V, V_{SS} = – 50 V Switch state is on V_S = V_D = ±45 V	25°C		10		pA
			85°C		40		
			125°C		170		

(1) When V_S is positive,V_D is negative. And when V_S is negative, V_D is positive.
(2) When V_S is at a voltage potential, V_D is floating. And when V_D is at a voltage potential, V_S is floating.

Copyright © 2022 Texas Instruments Incorporated

7.9 Electrical Characteristics (72-V Single Supply)

V_{DD} = +72 V ± 10%, V_{SS} = 0 V, GND = 0 V (unless otherwise noted)
Typical at T_A = 25℃ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0 V to +60 V I_D = –5 mA	25°C		38	48	Ω
			–40°C to +85°C			65	
			–40°C to +125°C			80	
ΔR_{ON}	On-resistance mismatch between channels	V_S = 0 V to +60 V I_D = –5 mA	25°C		0.65		Ω
			–40°C to +85°C			1.5	
			–40°C to +125°C			2.1	
$R_{ON\ FLAT}$	On-resistance flatness	V_S = 0 V to +60 V I_D = –5 mA	25°C		0.6		Ω
$R_{ON\ DRIFT}$	On-resistance drift	V_S = 0 V, I_S = –5 mA	–40°C to +125°C		0.25		Ω/°C
$I_{S(OFF)}$	Source off leakage current(1)	Switch state is off V_S = +60 V / 1 V V_D = 1 V / +60 V	25°C		0.02		nA
			–40°C to +85°C	–3		3	
			–40°C to +125°C	–15		15	
$I_{D(OFF)}$	Drain off leakage current(1)	Switch state is off V_S = +60 V / 1 V V_D = 1 V / +60 V	25°C		0.06		nA
			–40°C to +85°C	–8		8	
			–40°C to +125°C	–40		40	
$I_{S(ON)}$ $I_{D(ON)}$	Channel on leakage current(2)	Switch state is on V_S = V_D = 1 V / +60 V	25°C		0.07		nA
			–40°C to +85°C	–8		8	
			–40°C to +125°C	–40		40	
$\Delta I_{S(ON)}$ $\Delta I_{D(ON)}$	Leakage current mismatch between channels(2)	Switch state is on V_S = V_D = 1 V / +60 V	25°C		20		pA
			85°C		50		
			125°C		120		

(1) When V_S is 60 V, V_D is 1 V. Or when V_S is 1 V, V_D is 60 V.
(2) When V_S is at a voltage potential, V_D is floating. Or when V_D is at a voltage potential, V_S is floating.

Copyright © 2022 Texas Instruments Incorporated

7.10 Electrical Characteristics (100-V Single Supply)

V_{DD} = +100 V, V_{SS} = 0 V, GND = 0 V (unless otherwise noted)
Typical at T_A = 25℃ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0 V to +95 V I_D = –5 mA	25°C		38	48	Ω
			–40°C to +85°C			65	
			–40°C to +125°C			80	
ΔR_{ON}	On-resistance mismatch between channels	V_S = 0 V to +95 V I_D = –5 mA	25°C		0.65		Ω
			–40°C to +85°C			1.5	
			–40°C to +125°C			2.1	
$R_{ON\ FLAT}$	On-resistance flatness	V_S = 0 V to +95 V I_D = –5 mA	25°C		0.6		Ω
$R_{ON\ DRIFT}$	On-resistance drift	V_S = 0 V, I_S = –5 mA	–40°C to +125°C		0.25		Ω/°C
$I_{S(OFF)}$	Source off leakage current(1)	Switch state is off V_S = +95 V / 1 V V_D = 1 V / +95 V	25°C		0.02		nA
			–40°C to +85°C	–3		3	
			–40°C to +125°C	–15		15	
$I_{D(OFF)}$	Drain off leakage current(1)	Switch state is off V_S = +95 V / 1 V V_D = 1 V / +95 V	25°C		0.09		nA
			–40°C to +85°C	–8		8	
			–40°C to +125°C	–40		40	
$I_{S(ON)}$ $I_{D(ON)}$	Channel on leakage current(2)	Switch state is on V_S = V_D = 1 V / +95 V	25°C		0.1		nA
			–40°C to +85°C	–8		8	
			–40°C to +125°C	–40		40	
$\Delta I_{S(ON)}$ $\Delta I_{D(ON)}$	Leakage current mismatch between channels(2)	Switch state is on V_S = V_D = 1 V / +95 V	25°C		50		pA
			85°C		120		
			125°C		350		

(1) When V_S is 95 V, V_D is 1 V. Or when V_S is 1 V, V_D is 95 V.
(2) When V_S is at a voltage potential, V_D is floating. Or when V_D is at a voltage potential, V_S is floating.

Copyright © 2022 Texas Instruments Incorporated

7.11 Switching Characteristics: TMUX810x Devices

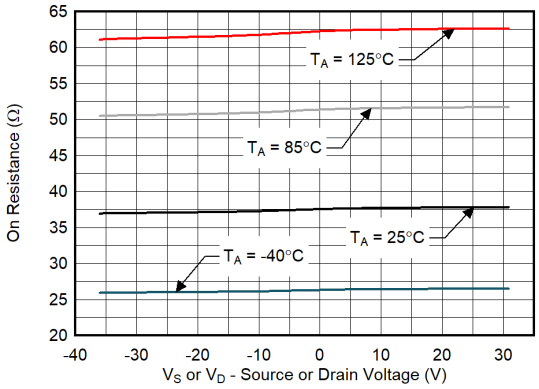
over operating free-air temperature range (unless otherwise noted)
typical at V_{DD} = +36 V, V_{SS} = – 36 V, GND = 0 V and T_A = 25℃ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
t_{TRAN}	Transition time from control input	V_S = 10 V R_L = 10 kΩ, C_L = 15 pF	25°C		3		µs
			– 40°C to +85°C			10	
			– 40°C to +125°C			12	
$t_{ON\ (EN)}$	Turn-on time from enable	V_S = 10 V R_L = 10 kΩ, C_L = 15 pF	25°C		3		µs
			– 40°C to +85°C			14	
			– 40°C to +125°C			15	
$t_{OFF\ (EN)}$	Turn-off time from enable	V_S = 10 V R_L = 10 kΩ, C_L = 15 pF	25°C		0.65		µs
			– 40°C to +85°C			3	
			– 40°C to +125°C			3	
t_{BBM}	Break-before-make time delay	V_S = 10 V, R_L = 10 kΩ, C_L = 15 pF	25°C		3		µs
			– 40°C to +85°C	0.1			
			– 40°C to +125°C	0.1			
$T_{ON\ (VDD)}$	Device turn on time (V_{DD} to output)	V_{DD} ramp rate = 1 V/µs, V_S = 10 V, R_L = 10 kΩ, C_L = 15pF	25°C		75		µs
t_{PD}	Propagation delay	R_L = 50 Ω, C_L = 5 pF	25°C		550		ps
Q_{INJ}	Charge injection	V_S = (V_{DD} + V_{SS}) / 2, C_L = 1 nF	25°C		– 150		pC
O_{ISO}	Off isolation	R_L = 50 Ω, C_L = 5 pF V_S = (V_{DD} + V_{SS}) / 2, f = 1 MHz	25°C		– 110		dB
X_{TALK}	Crosstalk	R_L = 50 Ω, C_L = 5 pF V_S = (V_{DD} + V_{SS}) / 2, f = 1MHz	25°C		– 110		dB
BW	– 3dB bandwidth (TMUX8108)	R_L = 50 Ω, C_L = 5 pF V_S = (V_{DD} + V_{SS}) / 2	25°C		200		MHz
BW	– 3dB bandwidth (TMUX8109)				380		
I_L	Insertion loss	R_L = 50 Ω, C_L = 5 pF V_S = (V_{DD} + V_{SS}) / 2, f = 1 MHz	25°C		– 2.8		dB
THD+N	Total harmonic distortion + Noise	Dual supply voltage V_{PP} = 5 V, V_{BIAS} = (V_{DD} + V_{SS}) / 2 R_L = 1 kΩ, C_L = 5 pF, f = 20 Hz to 20 kHz	25°C		0.003		%
$C_{S(OFF)}$	Source off capacitance	V_S = (V_{DD} + V_{SS}) / 2, f = 1 MHz	25°C		3		pF
$C_{D(OFF)}$	Drain off capacitance (TMUX8108)	V_S = (V_{DD} + V_{SS}) / 2, f = 1 MHz	25°C		20		pF
$C_{D(OFF)}$	Drain off capacitance (TMUX8109)	V_S = (V_{DD} + V_{SS}) / 2, f = 1 MHz	25°C		10		pF
$C_{S(ON)}$, $C_{D(ON)}$	On capacitance (TMUX8108)	V_S = (V_{DD} + V_{SS}) / 2, f = 1 MHz	25°C		21		pF
$C_{S(ON)}$, $C_{D(ON)}$	On capacitance (TMUX8109)	V_S = (V_{DD} + V_{SS}) / 2, f = 1 MHz	25°C		12		pF

Copyright © 2022 Texas Instruments Incorporated

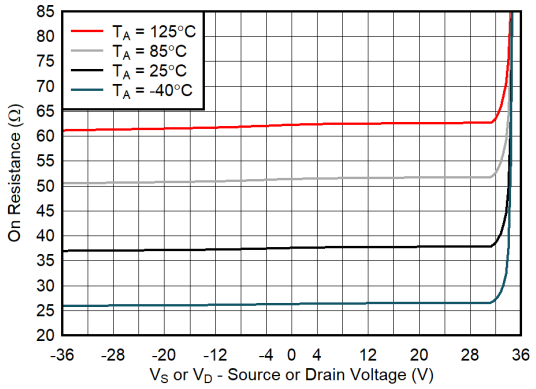
7.12 Typical Characteristics

at T_A = 25°C, V_{DD} = +36 V, and V_{SS} = – 36 V (unless otherwise noted)



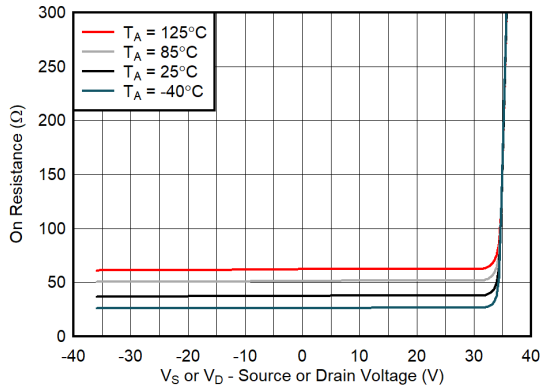
V_{DD} = 36 V, V_{SS} = – 36 V
Flatest Ron Region

图 7-1. On-Resistance vs Source or Drain Voltage



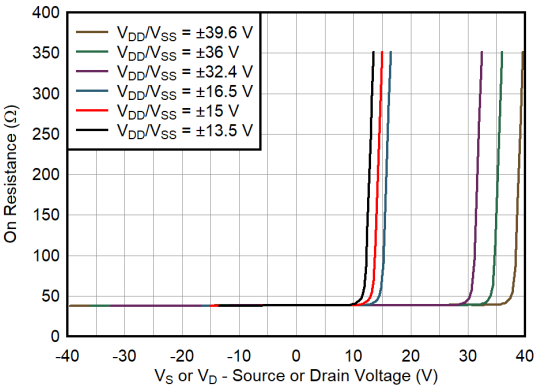
V_{DD} = 36 V, V_{SS} = – 36 V

图 7-2. On-Resistance vs Source or Drain Voltage



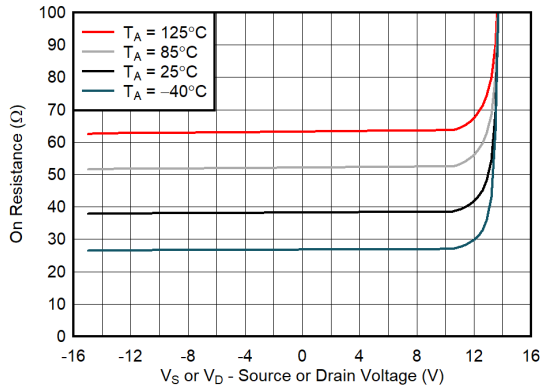
V_{DD} = 36 V, V_{SS} = – 36 V

图 7-3. On-Resistance vs Source or Drain Voltage



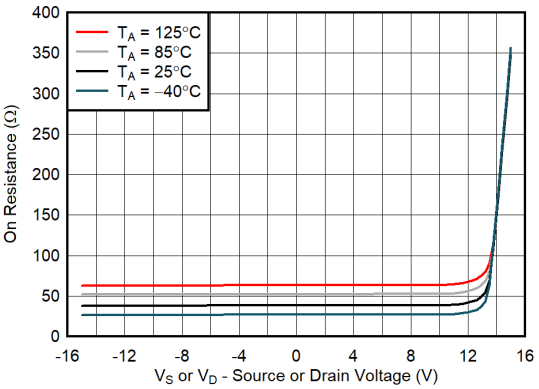
Dual Supply Voltages

图 7-4. On-Resistance vs Source or Drain Voltage



V_{DD} = 15 V, V_{SS} = – 15 V

图 7-5. On-Resistance vs Source or Drain Voltage



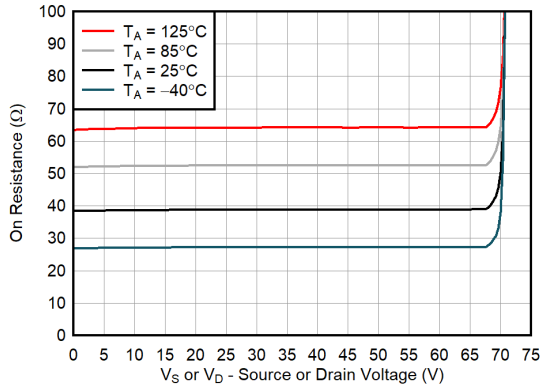
V_{DD} = 15 V, V_{SS} = – 15 V

图 7-6. On-Resistance vs Source or Drain Voltage

Copyright © 2022 Texas Instruments Incorporated

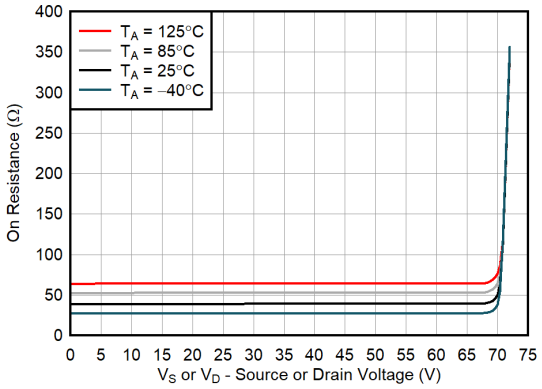
7.12 Typical Characteristics (continued)

at T_A = 25°C, V_{DD} = +36 V, and V_{SS} = – 36 V (unless otherwise noted)



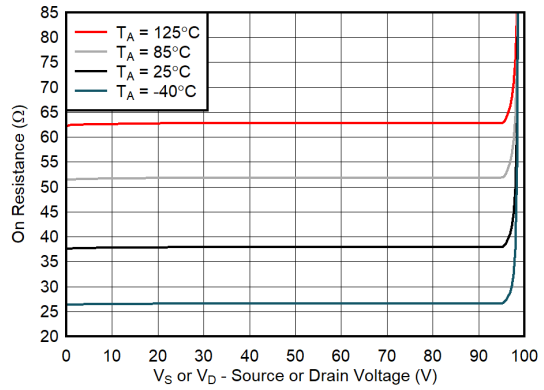
V_{DD} = 72 V, V_{SS} = 0 V

图 7-7. On-Resistance vs Source or Drain Voltage



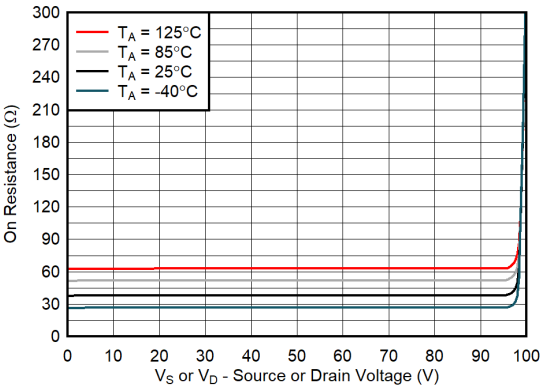
V_{DD} = 72 V, V_{SS} = 0 V

图 7-8. On-Resistance vs Source or Drain Voltage



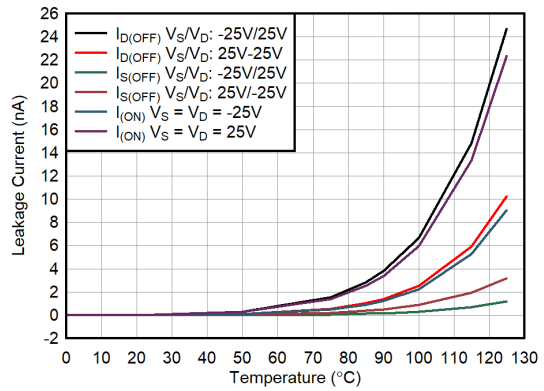
V_{DD} = 100 V, V_{SS} = 0 V

图 7-9. On-Resistance vs Source or Drain Voltage



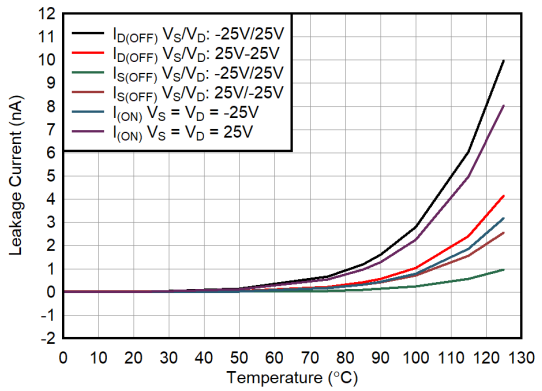
V_{DD} = 100 V, V_{SS} = 0 V

图 7-10. On-Resistance vs Source or Drain Voltage



V_{DD} = 36 V, V_{SS} = – 36 V
TMUX8108

图 7-11. Leakage Current vs Temperature



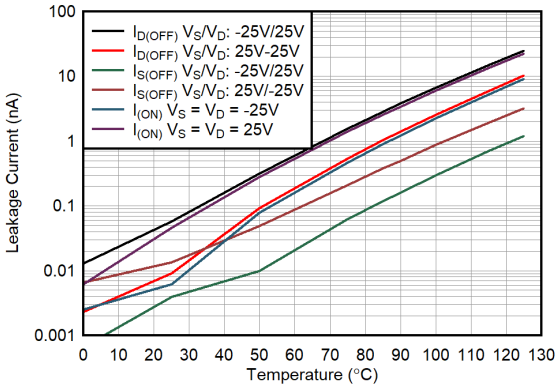
V_{DD} = 36 V, V_{SS} = – 36 V
TMUX8109

图 7-12. Leakage Current vs Temperature

Copyright © 2022 Texas Instruments Incorporated

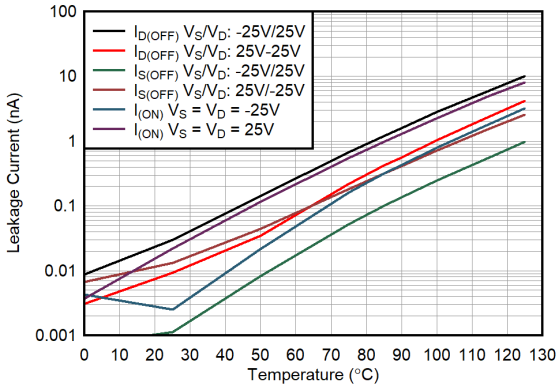
7.12 Typical Characteristics (continued)

at T_A = 25°C, V_{DD} = +36 V, and V_{SS} = – 36 V (unless otherwise noted)



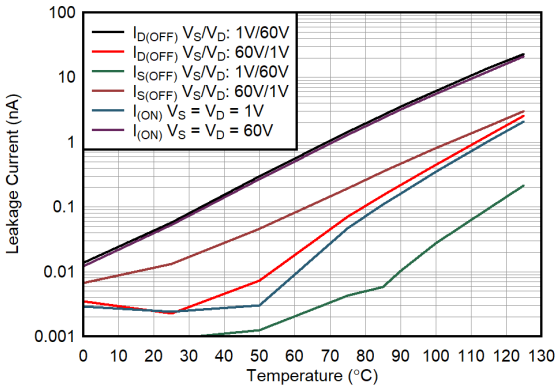
V_{DD} = 36 V, V_{SS} = – 36 V
TMUX8108

图 7-13. Leakage Current vs Temperature



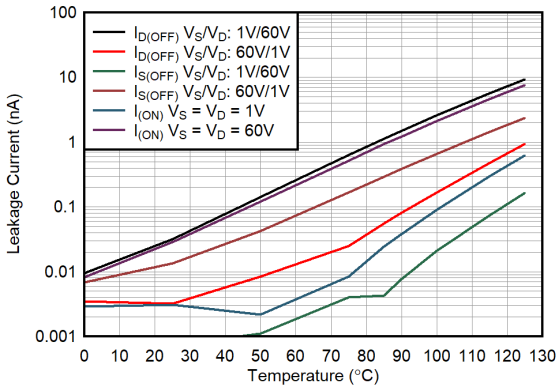
V_{DD} = 36 V, V_{SS} = – 36 V
TMUX8109

图 7-14. Leakage Current vs Temperature



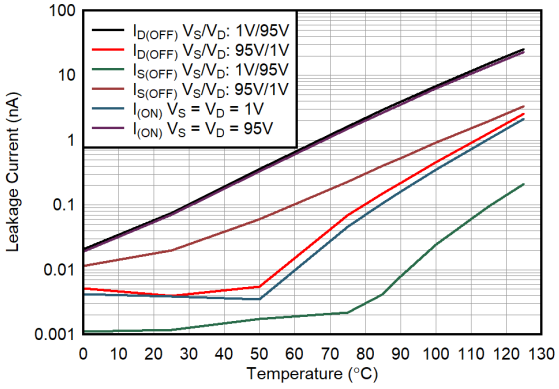
V_{DD} = 72 V, V_{SS} = 0 V
TMUX8108

图 7-15. Leakage Current vs Temperature



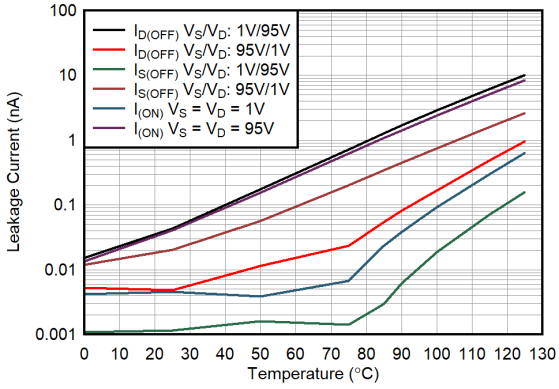
V_{DD} = 72 V, V_{SS} = 0 V
TMUX8109

图 7-16. Leakage Current vs Temperature



V_{DD} = 100 V, V_{SS} = 0 V
TMUX8108

图 7-17. Leakage Current vs Temperature



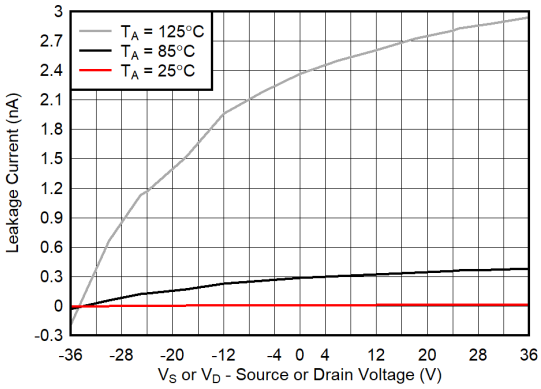
V_{DD} = 100 V, V_{SS} = 0 V
TMUX8109

图 7-18. Leakage Current vs Temperature

Copyright © 2022 Texas Instruments Incorporated

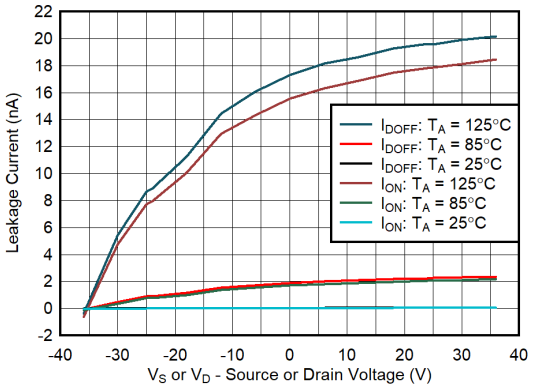
7.12 Typical Characteristics (continued)

at T_A = 25°C, V_{DD} = +36 V, and V_{SS} = – 36 V (unless otherwise noted)



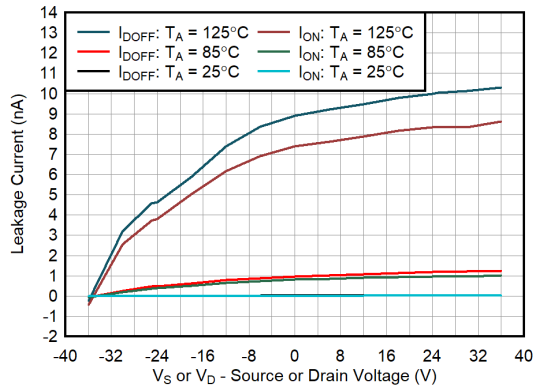
V_{DD} = 36 V, V_{SS} = – 36 V
TMUX8109 and TMUX8109

图 7-19. $I_{S(OFF)}$ Leakage Current vs Source or Drain Voltage



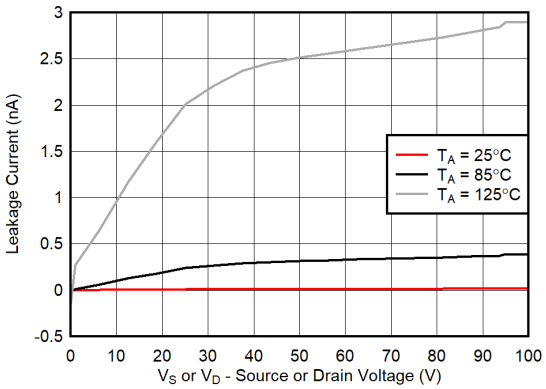
V_{DD} = 36 V, V_{SS} = – 36 V
TMUX8108

图 7-20. Leakage Current vs Source or Drain Voltage



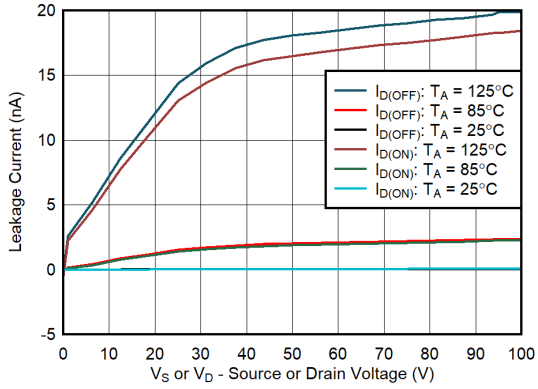
V_{DD} = 36 V, V_{SS} = – 36 V
TMUX8109

图 7-21. Leakage Current vs Source or Drain Voltage



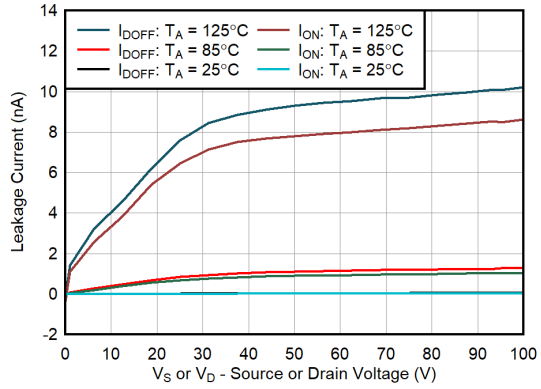
V_{DD} = 100 V, V_{SS} = 0 V
TMUX8108 and TMUX8109

图 7-22. $I_{S(OFF)}$ Leakage Current vs Source or Drain Voltage



V_{DD} = 100 V, V_{SS} = 0 V
TMUX8108

图 7-23. Leakage Current vs Source or Drain Voltage



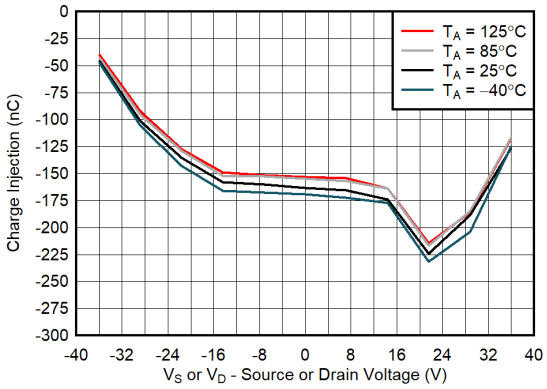
V_{DD} = 100 V, V_{SS} = 0 V
TMUX8109

图 7-24. Leakage Current vs Source or Drain Voltage

Copyright © 2022 Texas Instruments Incorporated

7.12 Typical Characteristics (continued)

at T_A = 25°C, V_{DD} = +36 V, and V_{SS} = – 36 V (unless otherwise noted)



V_{DD} = 36 V, V_{SS} = – 36 V

图 7-25. Charge Injection vs Source Voltage

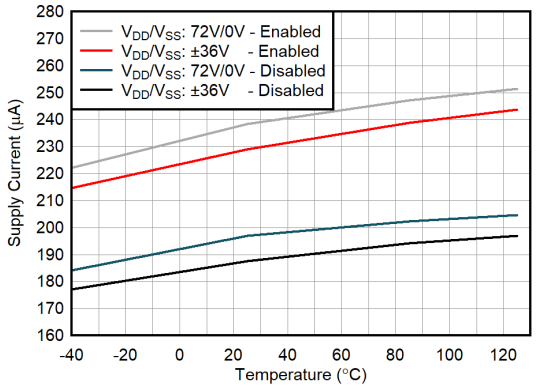
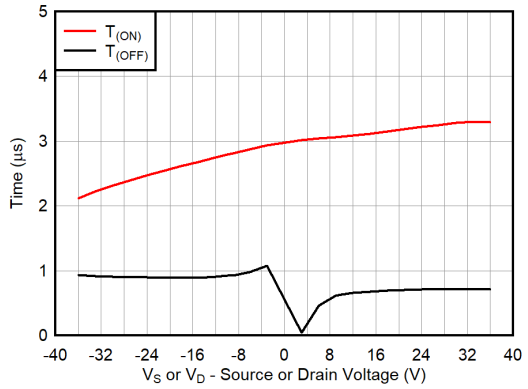
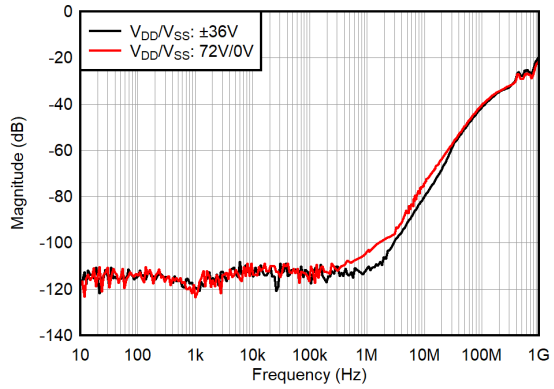


图 7-26. Supply Current vs Temperature



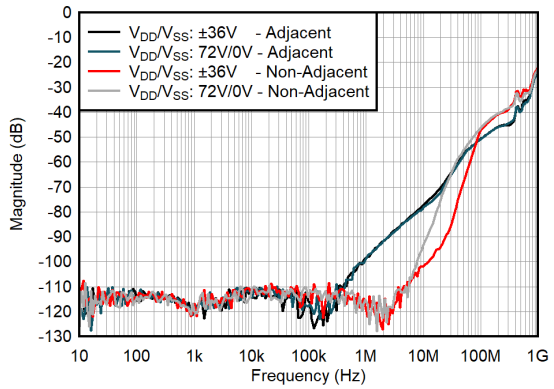
V_{DD} = 36 V, V_{SS} = – 36 V

图 7-27. Turn-On and Turn-Off Times vs Source Voltage



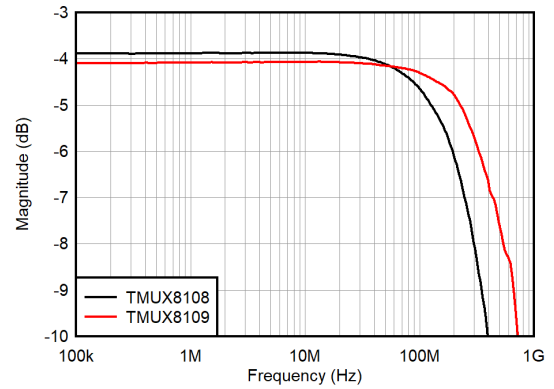
T_A = 25°C

图 7-28. Off Isolation vs Frequency



T_A = 25°C

图 7-29. Crosstalk vs Frequency



Bandwidth

图 7-30. Insertion Loss vs Frequency

Copyright © 2022 Texas Instruments Incorporated

8 Parameter Measurement Information

8.1 On-Resistance

The on-resistance of the TMUX8108 and TMUX8109 is the ohmic resistance across the source (Sx) and drain (Dx) pins of the device. The on-resistance varies with input voltage and supply voltage. 图 8-1 shows how the symbol R_{ON} is used to denote on-resistance. The measurement setup used to measure R_{ON} is shown in . ΔR_{ON} represents the difference between the R_{ON} of any two channels, while R_{ON_FLAT} denotes the flatness that is defined as the difference between the maximum and minimum value of on-resistance measured over the specified analog signal range.

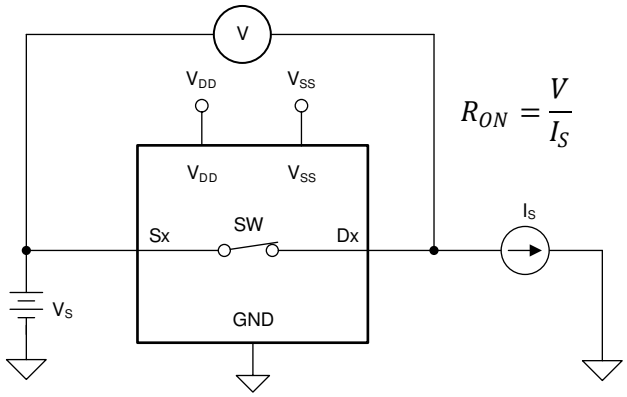


图 8-1. On-Resistance Measurement Setup

8.2 Off-Leakage Current

There are two types of leakage currents associated with a switch during the off state:

1. Source off-leakage current $I_{S(OFF)}$: the leakage current flowing into or out of the source pin when the switch is off.
2. Drain off-leakage current $I_{D(OFF)}$: the leakage current flowing into or out of the drain pin when the switch is off.

图 8-2 shows the setup used to measure both off-leakage currents.

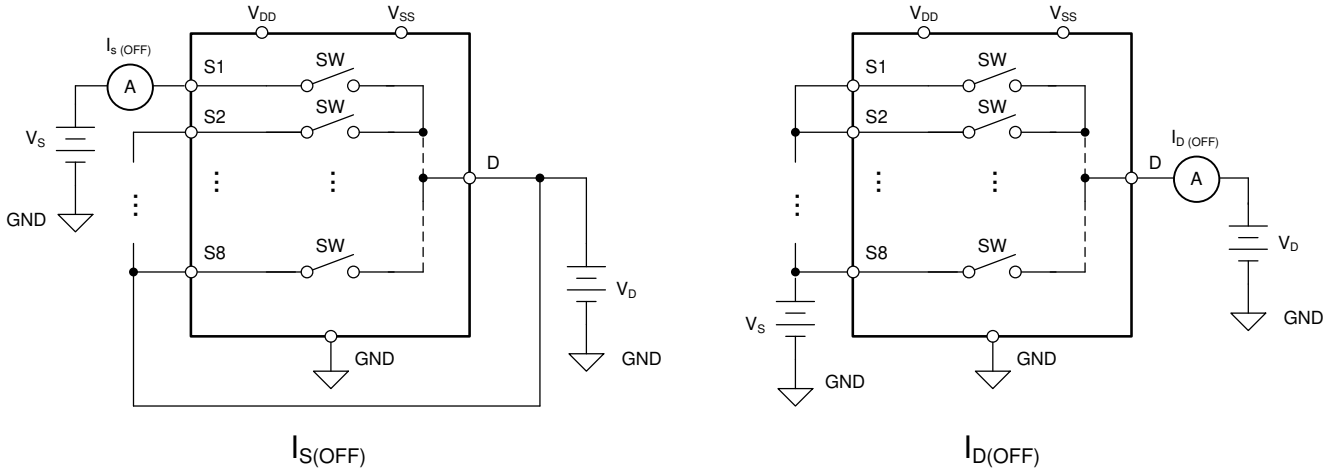


图 8-2. Off-Leakage Measurement Setup

8.3 On-Leakage Current

Source on-leakage current ($I_{S(ON)}$) and drain on-leakage current ($I_{D(ON)}$) denote the channel leakage currents when the switch is in the on state. $I_{S(ON)}$ is measured with the drain floating, while $I_{D(ON)}$ is measured with the source floating. 图 8-3 shows the circuit used for measuring the on-leakage currents.

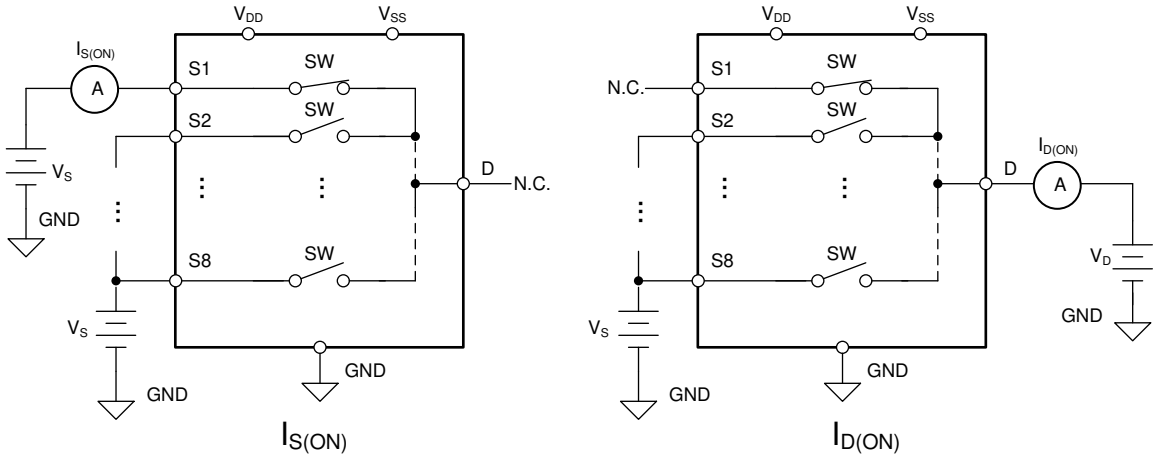


图 8-3. On-Leakage Measurement Setup

8.4 Break-Before-Make Delay

The break-before-make delay is a safety feature of the TMUX8108 and TMUX8109. The ON switches first break the connection before the OFF switches make connection. The time delay between the *break* and the *make* is known as break-before-make delay. 图 8-4 shows the setup used to measure break-before-make delay, denoted by the symbol t_{BBM}.

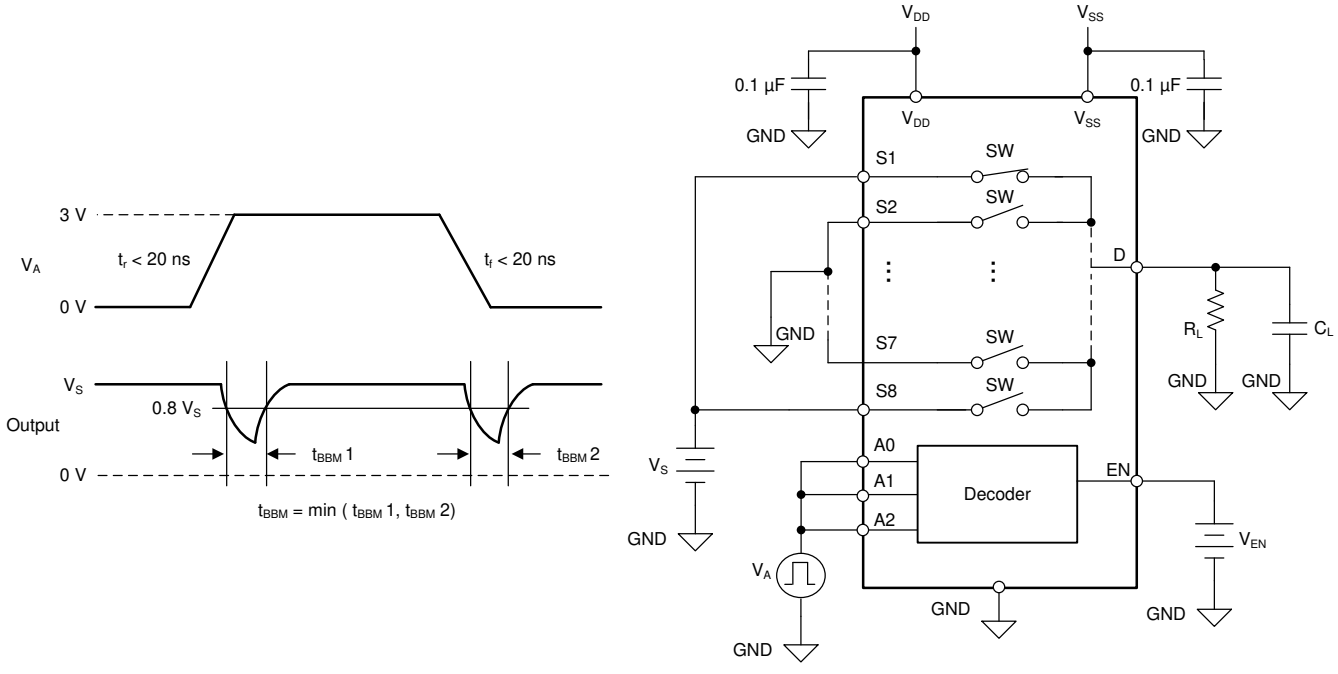


图 8-4. Break-Before-Make Delay Measurement Setup

Copyright © 2022 Texas Instruments Incorporated

8.5 Enable Turn-on and Turn-off Time

$t_{ON(EN)}$ time is defined as the time taken by the output of the TMUX8108 and TMUX8109 to rise to a 90% final value after the EN signal has risen to a 50% final value. $t_{OFF(EN)}$ is defined as the time taken by the output of the TMUX8108 and TMUX8109 to fall to a 10% final value after the EN signal has fallen to a 50% initial value. 图 8-5 shows the setup used to measure the enable delay time.

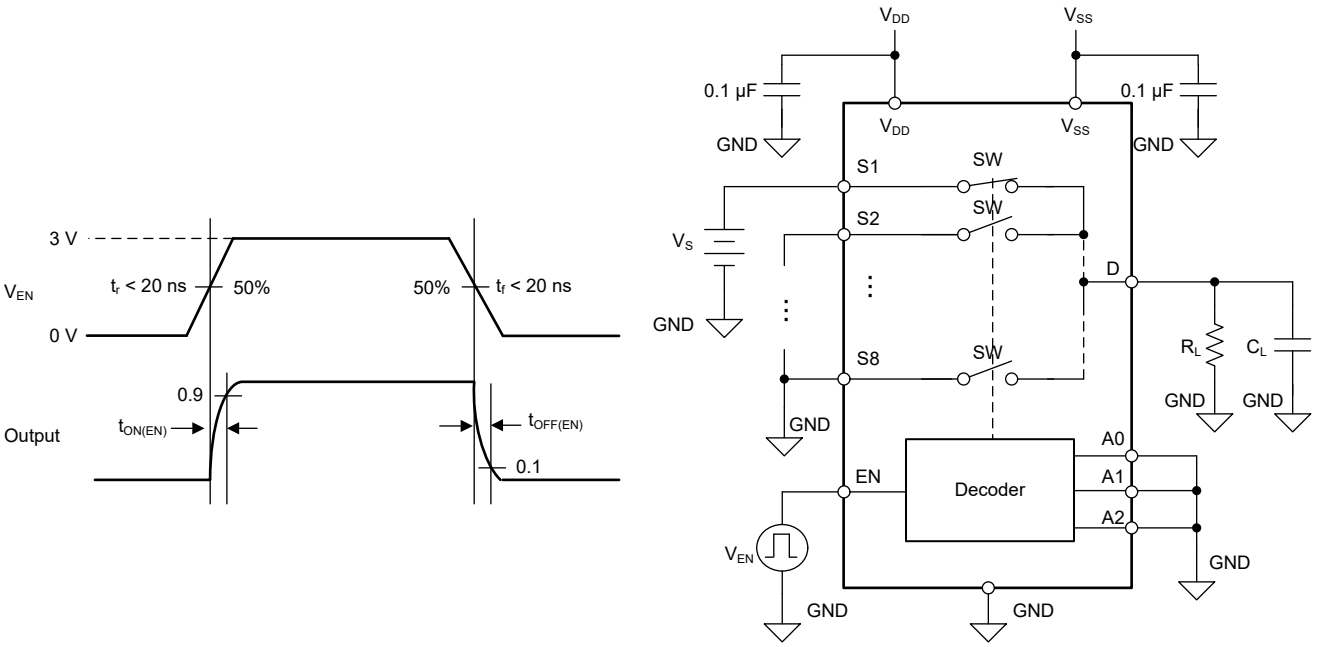


图 8-5. Enable Delay Measurement Setup

8.6 Transition Time

Transition time is defined as the time taken by the output of the device to rise (to 90% of the transition) or fall (to 10% of the transition) after the address signal (Ax) has fallen or risen to 50% of the transition. 图 8-6 shows the setup used to measure transition time, denoted by the symbol t_{TRAN}.

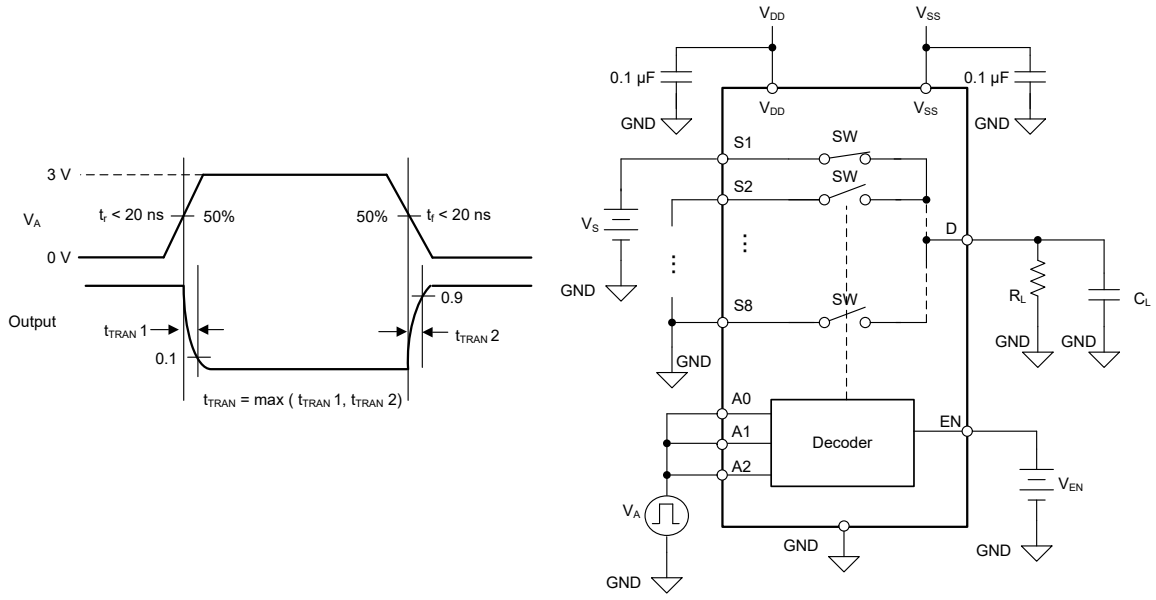


图 8-6. Transition Time Measurement Setup

8.7 Charge Injection

Charge injection is a measure of the glitch impulse transferred from the digital input to the analog output during switching, and is denoted by the symbol Q_{INJ}. 图 8-7 shows the setup used to measure charge injection from the source to drain.

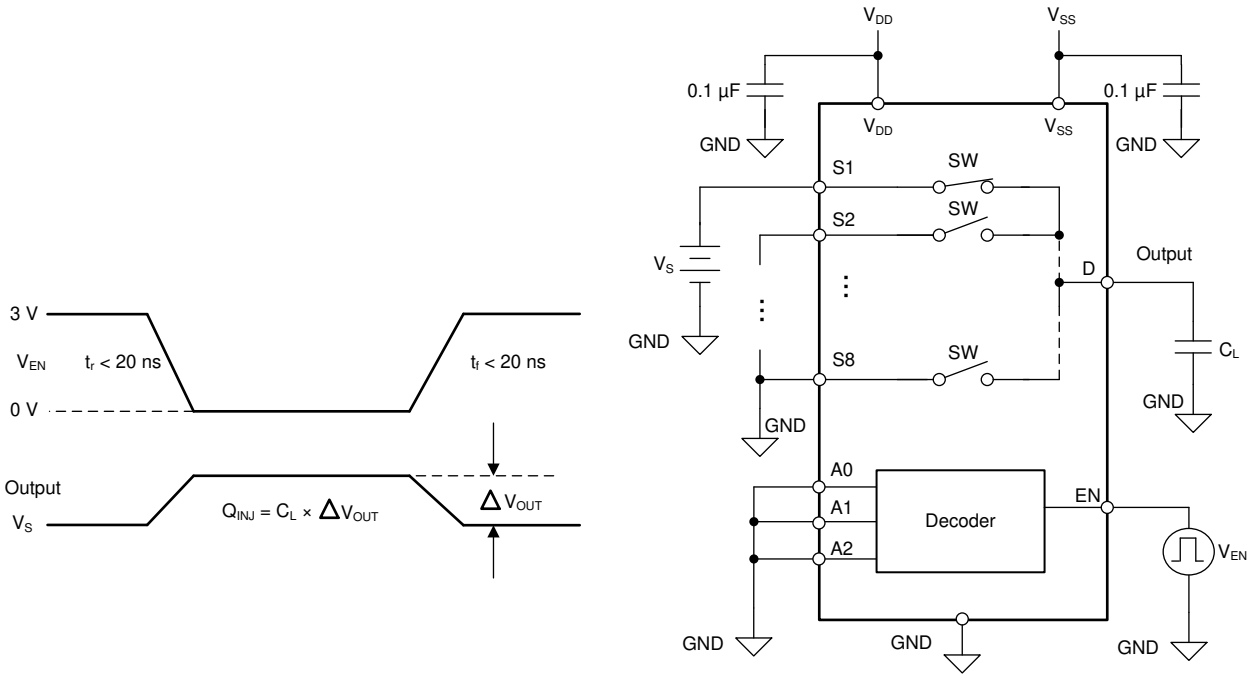
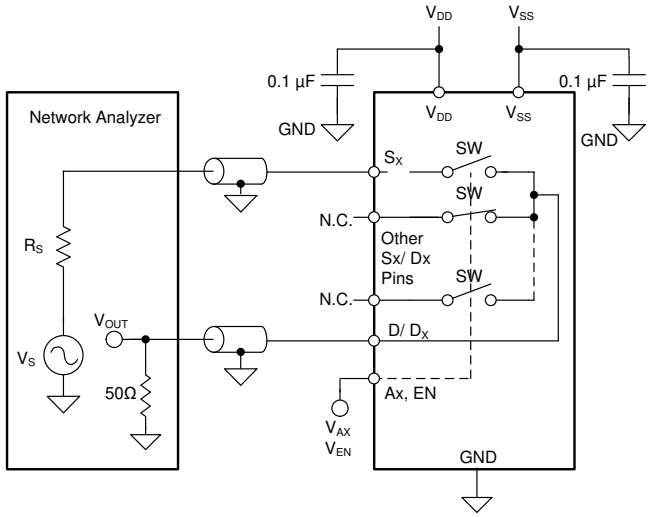


图 8-7. Charge-Injection Measurement Setup

8.8 Off Isolation

Off isolation is defined as the ratio of the signal at the drain pin (Dx) of the device when a signal is applied to the source pin (Sx) of an off-channel. The characteristic impedance for the measurement (Z_O) is 50 Ω. 图 8-8 shows the setup used to measure off isolation.

Copyright © 2022 Texas Instruments Incorporated



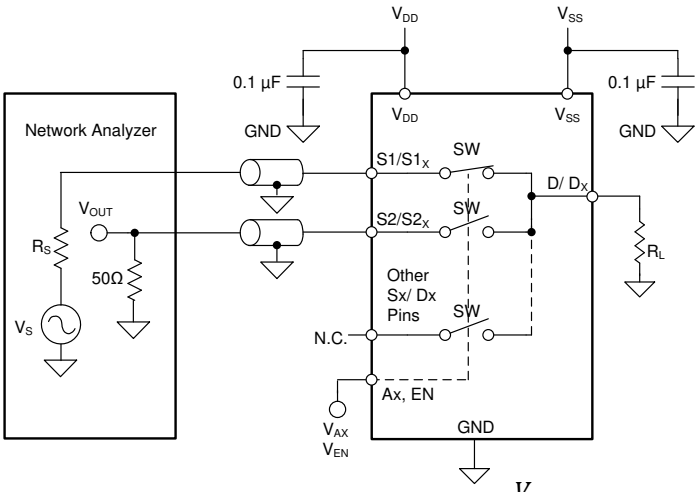
$$Off\ Isolation = 20 \times Log \frac{V_{OUT}}{V_S}$$

图 8-8. Off Isolation Measurement Setup

8.9 Crosstalk

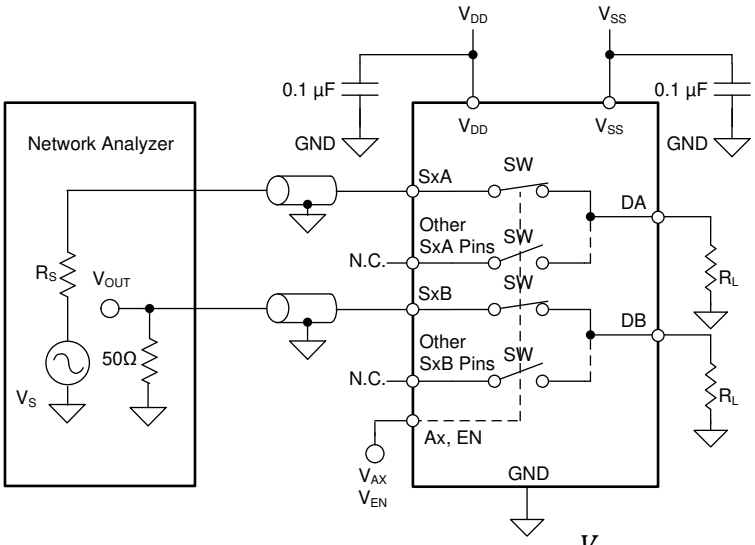
There are two types of crosstalk that can be defined for the devices:

1. Intra-channel crosstalk ($X_{TALK(INTRA)}$): the voltage at the source pin (Sx) of an off-switch input when a signal is applied at the source pin of an on-switch input in the same channel, as shown in 图 8-9 .
2. Inter-channel crosstalk ($X_{TALK(INTER)}$): the voltage at the source pin (Sx) of an on-switch input when a signal is applied at the source pin of an on-switch input in a different channel, as shown in 图 8-10. Inter-channel crosstalk applies only to the TMUX8109 device.



$$Intra-channel\ Crosstalk = 20 \times Log \frac{V_{OUT}}{V_S}$$

图 8-9. Intra-channel Crosstalk Measurement Setup

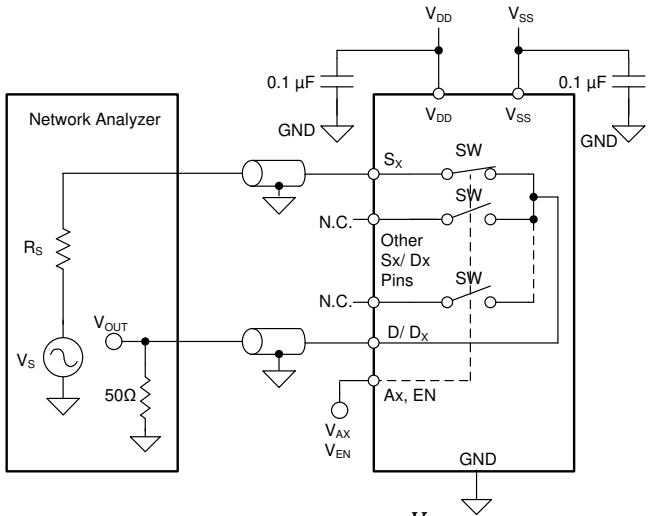


$$Inter-channel\ Crosstalk = 20 \times Log \frac{V_{OUT}}{V_S}$$

图 8-10. Inter-channel Crosstalk Measurement Setup

8.10 Bandwidth

Bandwidth (BW) is defined as the range of frequencies that are attenuated by < 3 dB when the input is applied to the source pin (Sx) of an on-channel, and the output is measured at the drain pin (D or Dx) of the TMUX810x. 图 8-11 shows the setup used to measure bandwidth of the switch.



$$Bandwidth = 20 \times Log \frac{V_{OUT}}{V_S}$$

图 8-11. Bandwidth Measurement Setup

8.11 THD + Noise

The total harmonic distortion (THD) of a signal is a measurement of the harmonic distortion and is defined as the ratio of the sum of the powers of all harmonic components to the power of the fundamental frequency at the multiplexer output. The on-resistance of the TMUX8108 and TMUX8109 varies with the amplitude of the input

Copyright © 2022 Texas Instruments Incorporated

signal and results in distortion when the drain pin is connected to a low-impedance load. Total harmonic distortion plus noise is denoted as THD+N. 图 8-12 shows the setup used to measure THD+N of the devices.

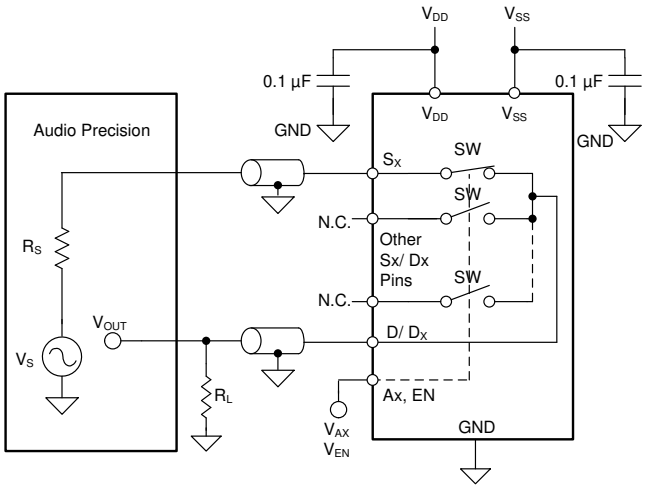


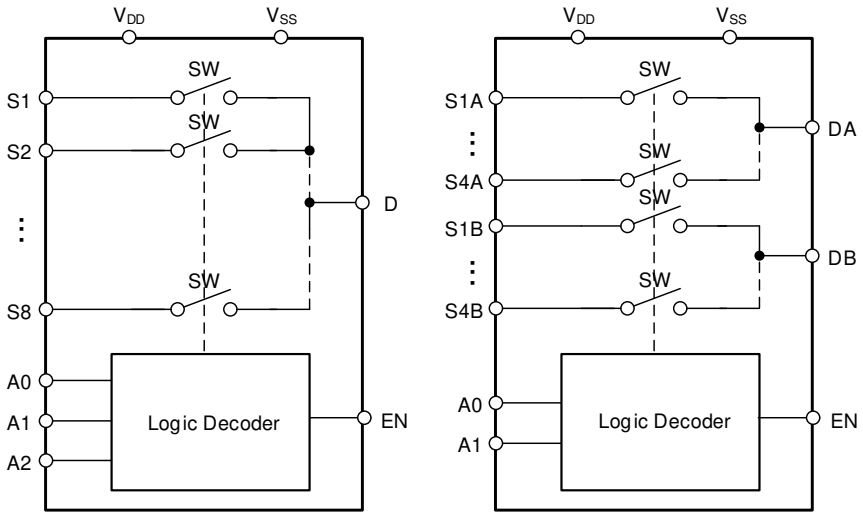
图 8-12. THD+N Measurement Setup

9 Detailed Description

9.1 Overview

The TMUX8108 and TMUX8109 are modern complementary metal-oxide semiconductor (CMOS) analog multiplexers in 8:1 (single ended) and 4:1 (differential) configurations. The devices work well with dual supplies, a single supply, or asymmetric supplies up to 100 V.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 Bidirectional Operation

The TMUX8108 and TMUX8109 conduct equally well from source (Sx) to drain (D or Dx) or from drain (D or Dx) to source (Sx). Each signal path has very similar characteristics in both directions.

9.3.2 Flat On – Resistance

The TMUX8108 and TMUX8109 are designed with a special switch architecture to produce ultra-flat on-resistance (R_{ON}) across most of the switch input operating region. The flat R_{ON} response allows the device to be used in precision sensor applications since the R_{ON} is controlled regardless of the signals sampled. The architecture is implemented without a charge pump so no unwanted noise is produced from the device to affect sampling accuracy.

The flatest on-resistance region extends from V_{SS} to roughly 5 V below V_{DD}. Once the signal is within 5 V of V_{DD} the on-resistance will exponentially increase and may impact desired signal transmission.

Copyright © 2022 Texas Instruments Incorporated

9.3.3 Protection Features

The TMUX8108 and TMUX8109 offer a number of protection features to enable robust system implementations.

9.3.3.1 Fail-Safe Logic

Fail-safe logic circuitry allows voltages on the logic control pins to be applied before the supply pins, protecting the device from potential damage. Additionaly the fail safe logic feature allows the logic inputs of the mux to be interfaced with high voltages, allowing for simplified interfacing if only high voltage control signals are present. The logic inputs are protected against positive faults of up to +48 V in powered-off condition, but do not offer protection against negative overvoltage condition.

Fail-safe logic also allows the devices to interface with a voltage greater than V_{DD} on the control pins during normal operation to add maximum flexibility in system design. For example, with a V_{DD} = 15 V, the logic control pins could be connected to +24 V for a logic high signal which allows different types of signals, such as analog feedback voltages, to be used when controlling the logic inputs. Regardless of the supply voltage, the logic inputs can be interfaced as high as 48 V.

9.3.3.2 ESD Protection

All pins on the TMUX8108 and TMUX8109 support HBM ESD protection level up to ±2 kV, which helps protect the devices from ESD events during the manufacturing process.

9.3.3.3 Latch-Up Immunity

Latch-up is a condition where a low impedance path is created between a supply pin and ground. This condition is caused by a trigger (current injection or overvoltage), but once activated the low impedance path remains even after the trigger is no longer present. This low impedance path may cause system upset or catastrophic damage due to excessive current levels. The latch-up condition typically requires a power cycle to eliminate the low impedance path.

In the TMUX8108 and TMUX8109 devices, an insulating oxide layer is placed on top of the silicon substrate to prevent any parasitic junctions from forming. As a result, the devices are latch-up immune under all circumstances by device construction.

The TMUX8108 and TMUX8109 devices are constructed on silicon on insulator (SOI) based process where an oxide layer is added between the PMOS and NMOS transistor of each CMOS switch to prevent parasitic structures from forming. The oxide layer is also known as an insulating trench and prevents triggering of latch up events due to overvoltage or current injections. The latch-up immunity feature allows the TMUX8108 and TMUX8109 to be used in harsh environments. For more information on latch-up immunity refer to *Using Latch Up Immune Multiplexers to Help Improve System Reliability*.

9.3.4 1.8 V Logic Compatible Inputs

The TMUX8108 and TMUX8109 devices have 1.8 V logic compatible control for all logic control inputs. 1.8 V logic level inputs allows the TMUX8108 and TMUX8109 to interface with processors that have lower logic I/O rails and eliminates the need for an external translator, which saves both space and bill of materials cost. For more information on 1.8 V logic implementations, refer to *Simplifying Design with 1.8 V logic Muxes and Switches*.

9.3.5 Integrated Pull-Down Resistor on Logic Pins

The TMUX8108 and TMUX8109 have internal weak pull-down resistors to GND to ensure the logic pins are not left floating. The value of this pull-down resistor is approximately 4 MΩ, but is clamped to about 1 µA at higher voltages. This feature integrates up to four external components and reduces system size and cost.

Copyright © 2022 Texas Instruments Incorporated

9.4 Device Functional Modes

9.4.1 Normal Mode

In Normal Mode operation, signals of up to V_{DD} and V_{SS} can be passed through the switch from source (Sx) to drain (D or Dx) or from drain (D or Dx) to source (Sx). 表 9-1 and 表 9-2 shows the address (Ax) pins and the enable (EN) pin determines which switch path to turn on. The following conditions must be satisfied for the switch to stay in the ON condition:

- The difference between the primary supplies (V_{DD} – V_{SS}) must be greater than or equal to 10 V. With a minimum V_{DD} of 10 V.
- The input signals on the source (Sx) or the drain (Dx) must be be between V_{DD} and V_{SS}.
- The logic control address pins (Ax) must have selected the switch path.

9.4.2 Truth Tables

表 9-1 shows the truth tables for the TMUX8108.

表 9-1. TMUX8108 Truth Table

EN	A2	A1	A0	Normal Condition
0	X(1)	X(1)	X(1)	None
1	0	0	0	S1
1	0	0	1	S2
1	0	1	0	S3
1	0	1	1	S4
1	1	0	0	S5
1	1	0	1	S6
1	1	1	0	S7
1	1	1	1	S8

(1) "X" means "do not care."

表 9-2 shows the truth tables for the TMUX8109.

表 9-2. TMUX8109 Truth Table

EN	A1	A0	Normal Condition
0	X(1)	X(1)	None
1	0	0	S1x
1	0	1	S2x
1	1	0	S3x
1	1	1	S4x

(1) "X" means "do not care."

If unused, address (Ax) pins must be tied to GND or Logic High in to ensure the device does not consume additional current as highlighted in *Implications of Slow or Floating CMOS Inputs*. Unused signal path inputs (Sx or Dx) should be connected to GND for best performance.

Copyright © 2022 Texas Instruments Incorporated

10 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

10.1 Application Information

The TMUX8108 and TMUX8109 are high voltage multiplexers capable of supporting analog and digital signals. The high voltage capability of these multiplexers allow them to be used in systems with high voltage signal swings or in systems with high common mode voltages.

Additionally, the TMUX810x devices provide consistent analog parametric performance across the entire supply voltage range allowing the devices to be powered by the most convient supply rails in the system while still providing excellent performance.

10.2 Typical Application

Many analog front end data acquistion systems are designed to support differential input signals with a wide range of output voltages. In systems where the output sensor is separated from the rest of the signal chain by long cables, a high common mode voltage shift can superimpose on the signal lines. One solution to this problem is to use a high voltage multiplexer in combination with a high voltage op amp level translation stage to properly scale the input signals to the correct input requirements of the ADC. The TMUX8109 allows the system to be designed for a differential, four channel, multiplexed data acquisition system.

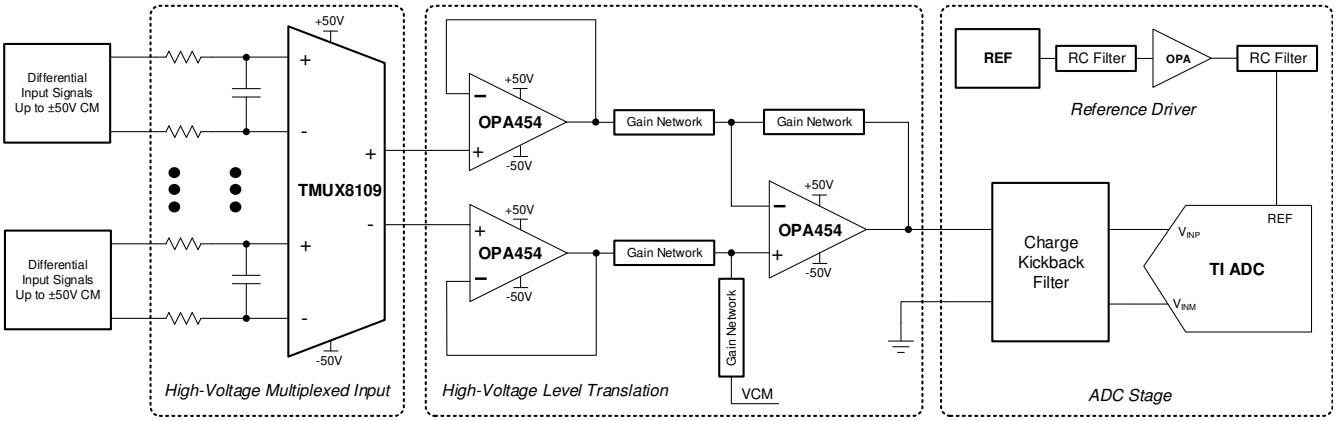


图 10-1. Typical Application

10.2.1 Design Requirements

表 10-1. Design Parameters

PARAMETER	VALUE
Positive supply (V_{DD}) mux and Op Amps	+50 V
Negative supply (V_{SS}) mux and Op Amps	-50 V
Maximum input / output signals with common mode shift	-50 V to 50 V
Mux control logic thresholds	1.8 V compatible, up to 48 V
Mux temperature range	-40°C to +125°C

10.2.2 Detailed Design Procedure

The multiplexed data aquistion circuit allows the system designer to have flexibility over both size and cost of the end product. Utilizing a multiplexer can reduce board size and cost by reducing the number of op amp circuits required for a multi-channel design. Additionally, the high voltage multiplexer can be paired with many implementations of high voltage level translation circuits such as difference amplifiers, instrumentation amplifiers, or fully differential amplifiers depending on the gain, noise requirements, and cost targets of the system.

In the example application, the TMUX8109 is paired with a difference amplifier and buffer stage op amps on both the positive and negative differential signals. Many data aquistion systems will place a buffer op amp following the mux for two reasons. The first reason is to eliminate the impact of the multiplexer on-resistance change across the signal range, preventing gain errors in the system. Secondly, depending on the output impedance of the sensors being interfaced, a high input impedance stage may be required to achieve system specification targets. The TMUX810x multiplexers have exceptionally flat on-resistance and low leakge currents across the signal voltage range and can potentially eliminate the need for buffer stage op amps depending on system requirements. Additionally, excellent crosstalk and off-isolation performance, paired with low capacitance ratings makes the TMUX810x multiplexers very flexible for system design of data aqusition systems.

A difference amplifier stage follows the multiplexer to eliminate the common mode voltage shift and can be used to scale the input signals to match the dynamic range of the selected ADC. In this example, both the op amp and multiplexer are rated for performance up to ±50 V. To find the maximum common mode voltage shift allowed, the system designer should take the maximum supply voltage and subtract the maximum voltage of the differential signal; the resulting voltage is the maximum common mode shift that can be accomodated without exceding the input voltage requirements of the multiplexer. The difference amplifier circuit relies on the matched resistor for good CMRR performance and typically has lower voltage gains and lower input impedances. If higher gains are required, or for better CMRR performance, an instrumentation amplifier can be swapped into the circuit. Both op amp solutions can be utilized to remove the common mode voltage offset and extract the true differential signal. The high voltage multiplexer at the front end of the design requires the system to have high voltage power supply rails to pass signals within V_{SS} and V_{DD}, this should be considered in the overal architecture of the system design. This multiplexed application becomes increasingly valuable with larger number of input channels by greatly reducing the total component count.

Copyright © 2022 Texas Instruments Incorporated

10.2.3 Application Curves

The example application utilizes the excellent leakage and crosstalk performance of the TMUX810x devices to reduce any impact introduced from a multiplexed system architecture. 图 10-2 shows the leakage current for both ON and OFF cases with a varrying temperature. 图 10-3 shows the excellent crosstalk performance of the TMUX810x devices. These features make the TMUX8108 and TMUX8109 an ideal solution for multiplexed data acquisition applications that require excellent linearity and low distortion.

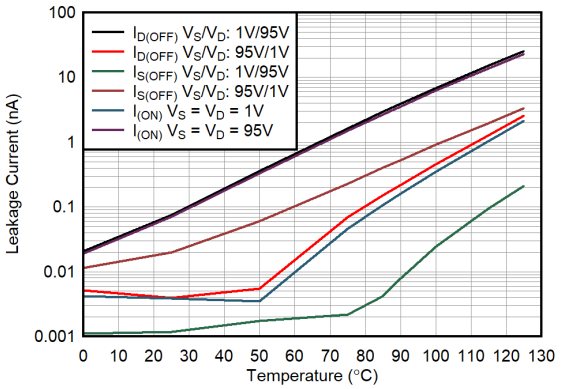


图 10-2. Leakage Current

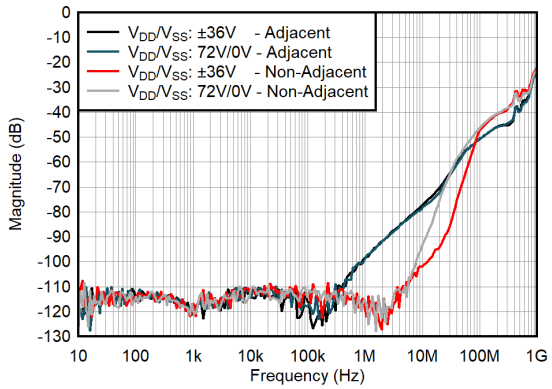


图 10-3. Crosstalk

11 Power Supply Recommendations

The TMUX8108 and TMUX8109 operate across a wide supply range of ±10 V to ±50 V (10 V to 100 V in single-supply mode). They also perform well with asymmetric supplies such as V_{DD} = 50 V and V_{SS}= – 10 V. For improved supply noise immunity, use a supply decoupling capacitor ranging from 1 µF to 10 µF at both the V_{DD} and V_{SS} pins to ground. An additional 0.1 µF capacitor placed closest to the supply pins will provide the best supply decoupling solution. Always ensure the ground (GND) connection is established before supplies are ramped.

12 Layout

12.1 Layout Guidelines

The following images illustrate an example of a PCB layout with the TMUX8108 and TMUX8109. Some key considerations are:

- For reliable operation, connect at least one decoupling capacitor ranging from 0.1 µF to 10 µF between V_{DD} and V_{SS} to GND. We recommend a 0.1 µF and 1 µF capacitor, placing the lowest value capacitor as close to the pin as possible. Make sure that the capacitor voltage rating is sufficient for the supply voltage.
- Keep the input lines as short as possible.
- Use a solid ground plane to help distribute heat and reduce electromagnetic interference (EMI) noise pickup.
- Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.

Copyright © 2022 Texas Instruments Incorporated

12.2 Layout Example

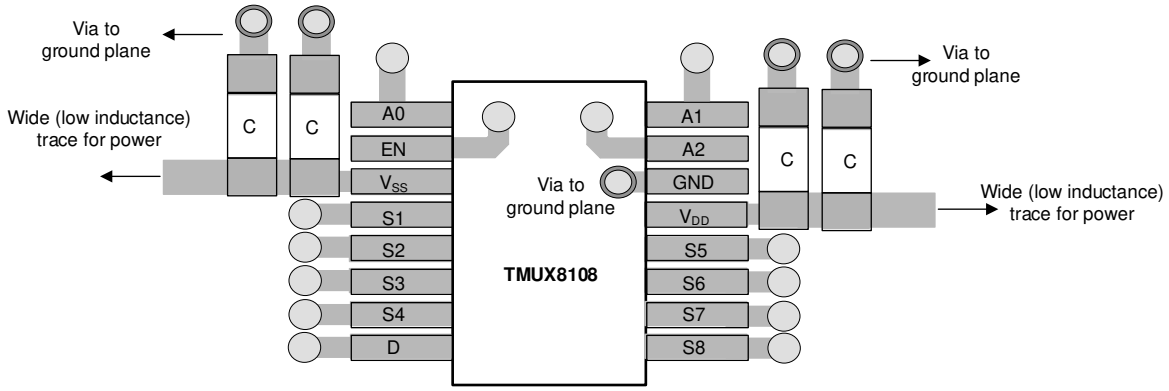


图 12-1. TMUX8108 TSSOP Layout Example

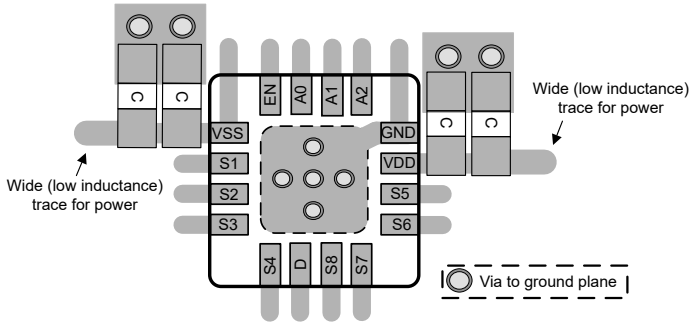


图 12-2. TMUX8108 QFN Layout Example

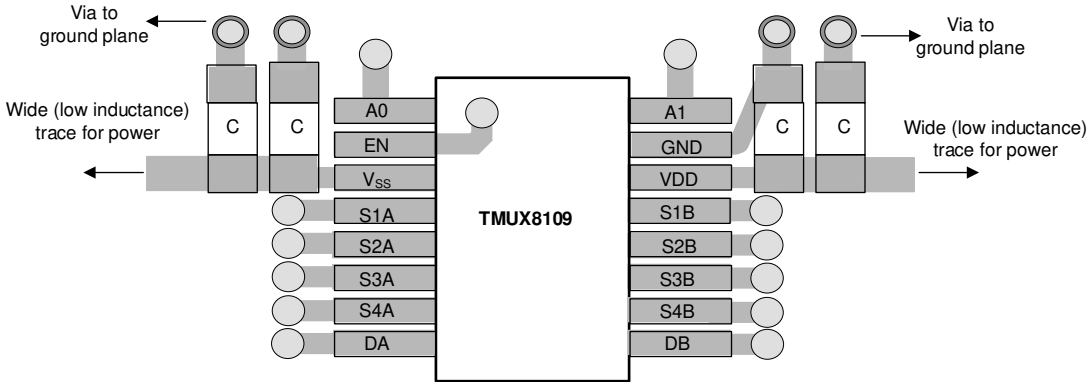


图 12-3. TMUX8109 TSSOP Layout Example

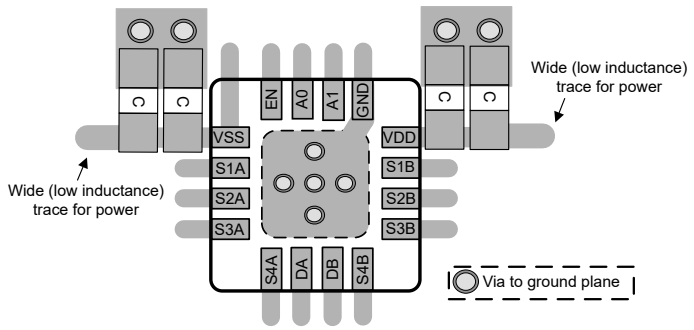


图 12-4. TMUX8109 QFN Layout Example

Copyright © 2022 Texas Instruments Incorporated

13 Device and Documentation Support

13.1 Documentation Support

13.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *Implications of Slow or Floating CMOS Inputs* application note
- Texas Instruments, *Multiplexers and Signal Switches Glossary* application report
- Texas Instruments, *Using Latch-Up Immune Multiplexers to Help Improve System Reliability* application report

13.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

13.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

13.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

13.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

13.6 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 2022 Texas Instruments Incorporated

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
PTMUX8108PWR	ACTIVE	TSSOP	PW	16	2000	TBD	Call TI	Call TI	-40 to 125		Samples
PTMUX8109PWR	ACTIVE	TSSOP	PW	16	2000	TBD	Call TI	Call TI	-40 to 125		Samples
TMUX8108PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TM8108	Samples
TMUX8109PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TM8109	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals.
TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

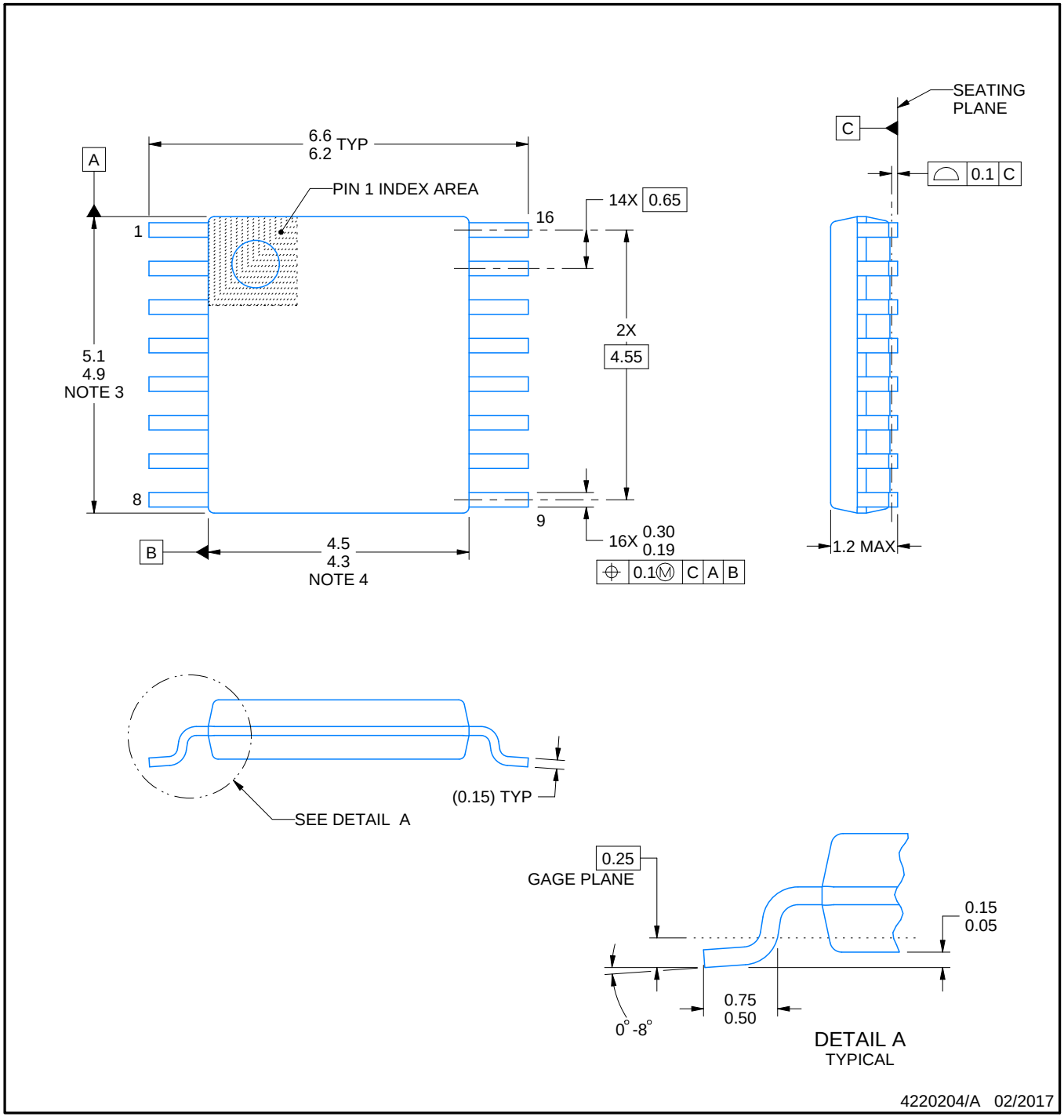
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE OUTLINE

PW0016A

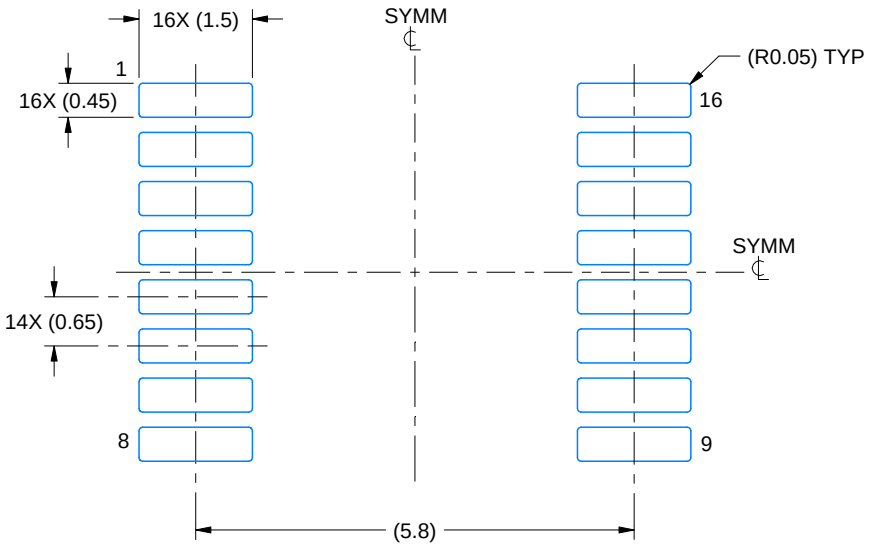
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

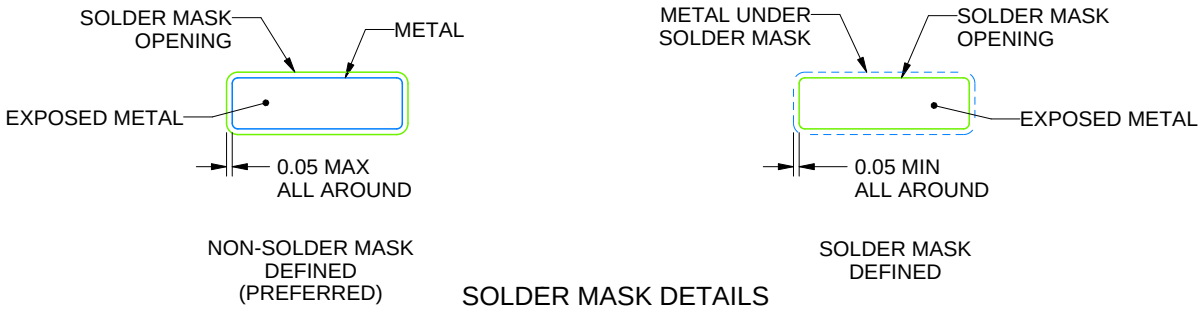


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

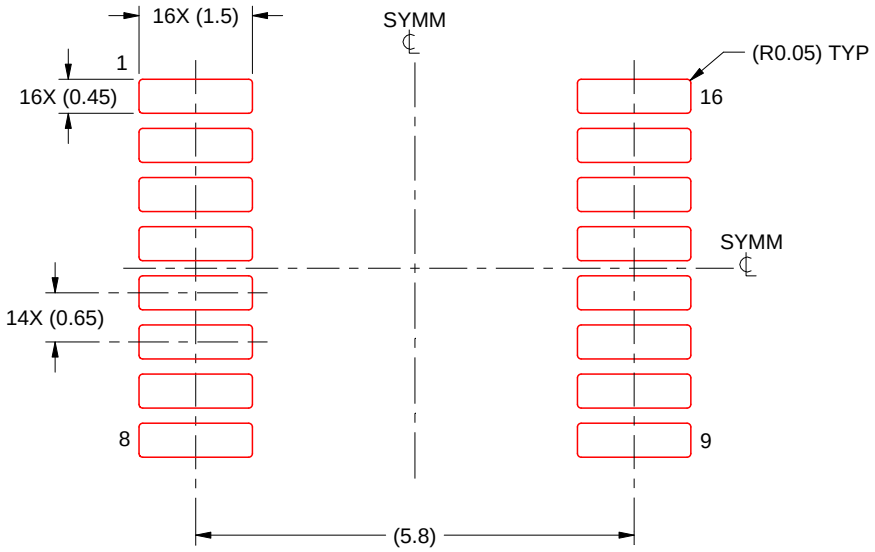


SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要声明和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 TI 的销售条款或 ti.com 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2022，德州仪器 (TI) 公司